

# EiceDRIVER™ 2EDR8259H, 2EDRx259X, 2EDRx258X

## Dual-channel isolated gate driver ICs in 300 mil DSO package

EiceDRIVER™ 2EDR8259H, 2EDRx259X, 2EDRx258X is a family of dual-channel isolated gate driver ICs, designed to drive Si and SiC MOSFETs and GaN HEMTs power switches. All products are available in a DSO package with 8 mm input-to-output creepage and provide reinforced isolation by means of on-chip coreless transformer (CT) technology. 2EDRx259X and 2EDRx258X variants in a 14-pin DSO package offer increased channel-to-channel creepage. They are suited for use in applications with higher bus voltage or higher pollution degree and, in general, can ease PCB routing. All versions offer optional shoot-through protection (STP) and dead-time control (DTC) functionality. This allows the operation as dual-channel low-side, dual-channel high-side or half-bridge gate driver with a configurable dead-time. With excellent common-mode transient immunity (CMTI), low part-to-part skew and fast signal propagation, the products are best suited for use in fast-switching power conversion systems.

### Features

- 2-channel isolated gate driver for Si and SiC MOSFETs and GaN HEMTs power switches
- Fast input-to-output propagation (38 ns) with excellent stability (+9/-5 ns)
- Strong output stage: 5 A/9 A source/ sink
- Fast output clamping for  $V_{DDA/B} < UVLO$
- Fast UVLO recovery time ( $< 2 \mu s$ )
- Four  $V_{DDA/B}$  UVLO options: 4 V, 8 V, 12 V, 15 V
- CMTI  $> 150$  V/ns
- Available in 16/14-pin 300 mil DSO package

### Isolation and safety certificates

- UL1577 with  $V_{ISO} = 5700 V_{RMS}$  (certification n. E311313)
- VDE0884-11 with  $V_{IOTM} = 8000 V_{pk}$ ,  $V_{IORM} = 1767 V_{pk}$ ,  $V_{IOSM} = 6875 V_{pk}$  (certification n. 40052310)
- IEC 60747-17 (certification n. 40055138)
- IEC62368-1 (certification n. 40052310, appendix 500Z1)

### Product validation

Fully qualified for industrial applications

Table 1

Portfolio

Part number	UVLO	EN/DIS	Package
2EDR8259H	8 V	DIS	DSO16-300mil
2EDR7259X	4 V	DIS	DSO14-300mil
2EDR8259X	8 V	DIS	DSO14-300mil
2EDR9259X	15 V	DIS	DSO14-300mil
2EDR8258X	8 V	EN	DSO14-300mil
2EDR6258X	12 V	EN	DSO14-300mil
2EDR9258X	15 V	EN	DSO14-300mil

### Potential applications

- Server, telecom SMPS
- EV Off-board chargers
- Low-voltage drives and power tools
- Solar micro inverter, solar optimizer
- Industrial power supply (SMPS, Residential UPS)

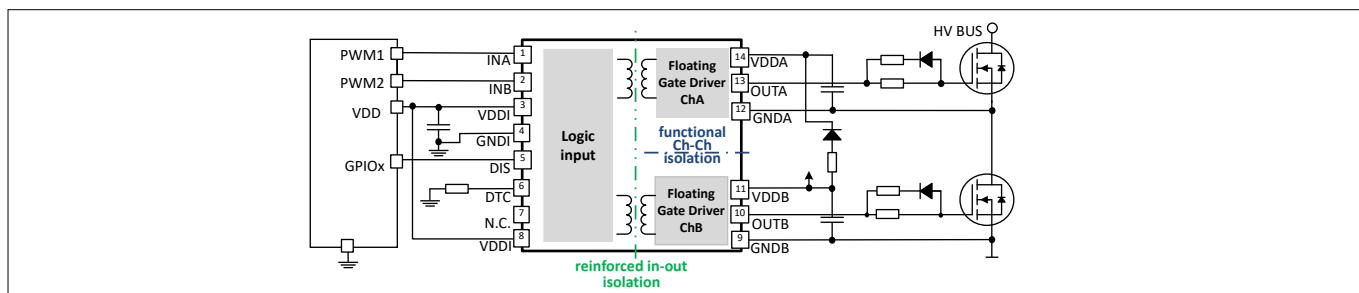


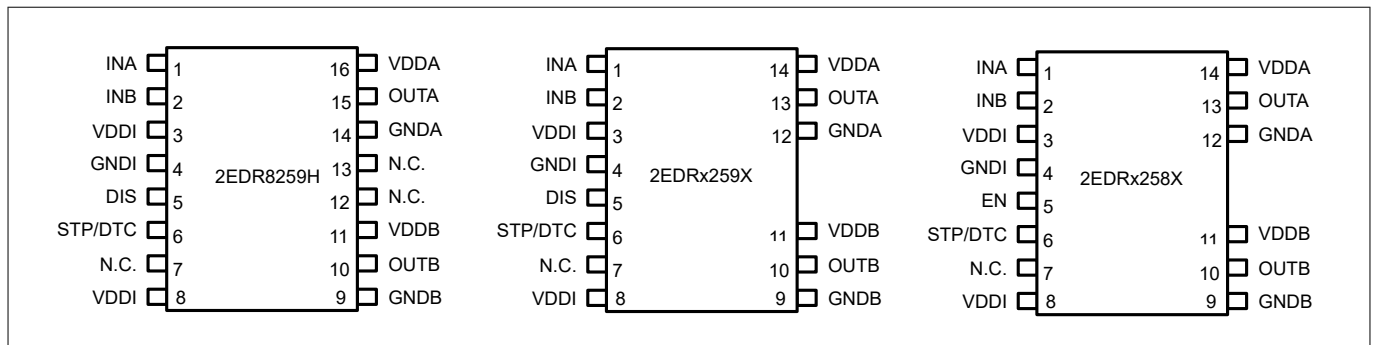
Figure 1 Application diagram

## Table of contents

	<b>Table of contents</b> .....	2
<b>1</b>	<b>Pin configuration and description</b> .....	3
<b>2</b>	<b>Functional description</b> .....	5
2.1	Block diagram .....	5
2.2	Power supply and Undervoltage Lockout (UVLO) .....	5
2.2.1	Input supply voltage .....	5
2.2.2	Output supply voltage .....	5
2.3	Input stage - INA, INB, DISABLE .....	6
2.4	Shoot-through protection and configurable dead-time - STP/DTC .....	8
2.5	Gate driver outputs .....	9
2.6	Fast active output clamping in UVLO conditions .....	9
2.7	CT communication and input to output data transmission .....	9
<b>3</b>	<b>Electrical characteristics</b> .....	10
3.1	Absolute maximum ratings .....	10
3.2	Thermal characteristics .....	11
3.3	Operating range .....	12
3.4	Electrical characteristics .....	12
3.5	Isolation specifications .....	17
<b>4</b>	<b>Timing diagrams</b> .....	20
<b>5</b>	<b>Typical characteristics</b> .....	23
<b>6</b>	<b>Package outline dimensions</b> .....	29
6.1	Device numbers and markings .....	29
6.2	Package DSO16-300mil .....	29
6.3	Package DSO14-300mil .....	31
<b>7</b>	<b>Revision history</b> .....	33
	<b>Disclaimer</b> .....	34

## 1 Pin configuration and description

### 1 Pin configuration and description



**Figure 2** Pin configuration (top side view)

**Table 2** Pin description

Pin 16-pin	Pin 14-pin	Symbol	Description
1	1	INA	<b>Input signal channel A</b> Logic input with TTL compatible thresholds and internal pull-down resistor
2	2	INB	<b>Input signal channel B</b> Logic input with TTL compatible thresholds and internal pull-down resistor
3,8	3,8	VDDI	<b>Input-side supply voltage</b> (operating range: 3 V to 17 V)
4	4	GNDI	<b>Ground primary-side</b>
5	5	DIS/ EN	<b>Disable input channel A and B</b> (active high) If DIS is low or left open, OUTA/OUTB are controlled by INA/INB DIS high causes OUTA/OUTB low <b>ENABLE input channel A and B</b> (active high) If EN is high, OUTA/OUTB are controlled by INA/INB EN low or left open causes OUTA/OUTB low
6	6	STP/DTC	<b>Shoot-through Protection (STP) and Dead-Time Control (DTC)</b> If STP/DTC is high or left open, OUTA and OUTB can overlap (SPT and DTC disabled). If STP/DTC is connected to GNDI with a resistance $R_{DTC}$ , OUTA and OUTB cannot overlap and a “safe dead-time” can be configured: $t_{dt} [ns] = 10 \times R_{DTC} [k\Omega]$ If STP/DTC is connected to GNDI, OUTA and OUTB cannot overlap (STP only enabled) Connecting capacitors to the DTC pin must be avoided.
7,12,13	7	N.C.	No internal connection
9	9	GNDB	<b>Ground secondary-side channel B</b>
10	10	OUTB	<b>Output secondary-side channel B</b> Low-impedance output with source and sink capability
11	11	VDDB	<b>Supply secondary-side channel B</b> (operating range: UVLO to 20 V)
14	12	GNDA	<b>Ground secondary-side channel A</b>

(table continues...)

## 1 Pin configuration and description

**Table 2** (continued) Pin description

Pin 16-pin	Pin 14-pin	Symbol	Description
15	13	OUTA	<b>Output secondary-side channel A</b> Low-impedance output with source and sink capability
16	14	VDDA	<b>Supply secondary-side channel A</b> (operating range: UVLO to 20 V)

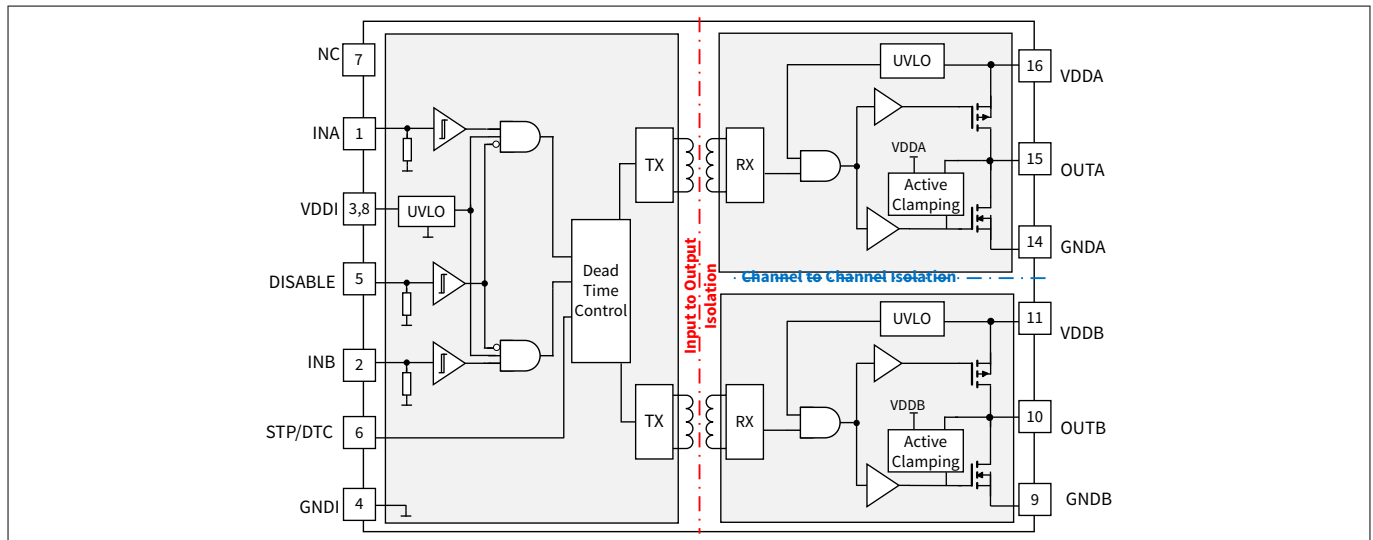
For package drawing details see [Chapter 6](#).

## 2 Functional description

## 2 Functional description

### 2.1 Block diagram

A simplified functional block diagram for EiceDRIVER™ 2EDR8259H, 2EDRx259X is given in Figure 3.



**Figure 3** Block diagram

### 2.2 Power supply and Undervoltage Lockout (UVLO)

Due to the input-to-output and channel-to-channel isolation, three power domains with independent power management are required. Undervoltage Lockout (UVLO) functions for both input and output supplies ensure a defined startup and robust functionality under all operating conditions.

#### 2.2.1 Input supply voltage

The input die is powered via VDDI and supports a wide supply voltage range from 3 V to 17 V. A ceramic bypass capacitor must be placed between VDDI and GNDI in close proximity to the device; a minimum bypass capacitance of 100 nF is recommended.

Power consumption to some extent, depends on switching frequency, as the input signal is converted into a train of repetitive current pulses to drive the coreless transformer. Due to the chosen robust encoding scheme the average repetition rate of these pulses and thus the average supply current depends on the switching frequency,  $f_{sw}$ . However, for  $f_{sw} < 500$  kHz this effect is very small.

The Undervoltage Lockout function for the input supply  $V_{DDI}$  ensures that, as long as  $V_{DDI}$  is below UVLO (e.g. in startup), no data is transferred to the output side and the gate driver output is held low (safety Lock-down at startup). When  $V_{DDI}$  exceeds the UVLO level, the PWM input signal is transferred to the output side. If the output side is ready (not in UVLO condition), the output reacts according to the logic input.

#### 2.2.2 Output supply voltage

The two output dies are powered via two independent supply voltages  $V_{DDA}$  and  $V_{VDB}$  (up to 20 V).

Two ceramic bypass capacitors must be placed between VDDA and GNDA and between VDDB and GNDB in close proximity to the device. A minimum capacitance of  $20 \times C_{iss}$  (MOSFET input capacitance) is recommended to ensure an acceptable ripple (5% of  $V_{DDO}$ ) on the supply pin.

The minimum supply voltage is set by the Undervoltage Lockout (UVLO) function. The gate driver output can be switched only if the output supply voltage ( $V_{DDA}$ ,  $V_{VDB}$ ) exceeds the output-side UVLO. Thus, it can be guaranteed that the switch transistor is not operated if the driving voltage is too low to achieve a complete and fast transition to the "on" state. Low driving voltage, in fact, could cause the power MOSFET to enter its saturation (ohmic) region with potentially destructive power dissipation; the output UVLO ensures that the

## 2 Functional description

switch transistor always stays within its Safe Operating Area (SOA). Versions with 4 V, 8 V, 12 V and 15 V UVLO thresholds for the output supply are currently available. [Table 3](#) shows the recommended UVLO levels for different Infineon power switch families.

**Table 3 Recommended UVLO levels for typical use-cases**

Inputs	Examples of part number	Recommended driver
Logic level OptiMOS™	BSC010N04LS6, BSZ070N08LS5, ..	2EDR7259 (4 V UVLO)
Normal level OptiMOS™	BSC040N10NS5, BSZ084N08NS5, ..	2EDR825x (8 V UVLO)
CoolMOS™	IPP60R099C7, IPB60R600P6, ..	2EDR825x (8 V UVLO)
650 V CoolSiC™	IMZA65R027M1H, IMW65R107M1H, ..	2EDR6258/ 2EDR925x (12/15 V UVLO)
650 V CoolGaN™	IGOT60R070D1, IGLD60R070D1, ..	2EDR7259 (4 V UVLO for unipolar driving) 2EDR825x (8 V UVLO for bipolar driving)

### 2.3 Input stage - INA, INB, DISABLE

The inputs INA and INB control two independent PWM channels. The input signal is transferred non-inverted to the corresponding gate driver outputs OUTA and OUTB. All inputs are compatible with LV-TTL threshold levels and provide a hysteresis of typically 0.8 V. The hysteresis is independent of the supply voltage  $V_{DDI}$ .

The PWM inputs are internally pulled down to a logic low voltage level (GNDI). In case the PWM-controller signals have an undefined state during the power-up sequence, the gate driver outputs are forced to the "off"-state (low).

If the DIS/EN input is at high/low state, this unconditionally drives both channel outputs to low state regardless of the state of INA or INB.

[Table 4](#) and [Table 5](#) shows the INA, INB, DIS/EN driver logic in case of sufficiently high supply voltage. Otherwise the outputs of the driver are determined by the Undervoltage Lockout (UVLO) and Output Active Clamping functionalities as shown in [Table 8](#).

**Table 4 Logic table in case of sufficient bias power - INA, INB, DIS**

Inputs		DIS	Supplies	Outputs		Note
INA	INB		$V_{DDI}$ , $V_{DDA}$ , $V_{ddb}$	OUTA	OUTB	
L	L	L or left open	> $UVLO_{VDDx,on}$ (active)	L	L	–
L	H	L or left open		L	H	–
H	H	L or left open		H	H	DTC/STP pin tied to $V_{DDI}$ or left open
				L	L	DTC/STP pin tied to GNDI via $R_{DTC}$
Left open	Left open	L or left open		L	L	Input pins internally pulled down
x	x	H		L	L	Outputs disabled via DIS high

## 2 Functional description

**Table 5**                      **Logic table in case of sufficient bias power - INA, INB, EN**

Inputs		EN	Supplies	Outputs		Note
INA	INB		$V_{DDI}$ , $V_{DDA}$ , $V_{DDB}$	OUTA	OUTB	
L	L	H	> $UVLO_{VDDx,on}$ (active)	L	L	–
L	H	H		L	H	–
H	H	H		H	H	DTC/STP pin tied to $V_{DDI}$ or left open
				L	L	DTC/STP pin tied to GNDI via $R_{DTC}$
Left open	Left open	H		L	L	Input pins internally pulled down
x	x	L or left open		L	L	Outputs disabled via EN low

## 2 Functional description

### 2.4 Shoot-through protection and configurable dead-time - STP/DTC

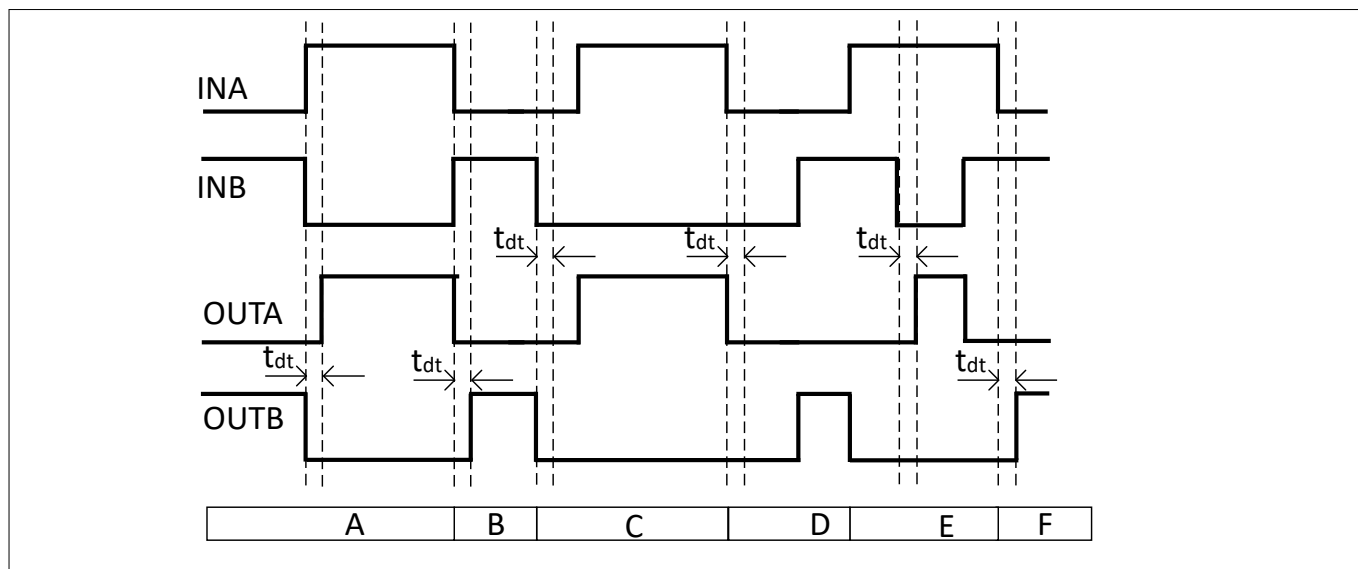
The shoot-through protection pulls down the outputs OUTA and OUTB when both input signals INA, INB are at high state. Its activation is recommended when the driver is used as half-bridge driver to prevent dangerous shoot-through due to unwanted overlap of INA and INB. A dead-time can be ensured and configured via pin STP/DTC as shown in Table 6.

**Table 6 STP/DTC logic table**

Conditions on the STP/DTC pin	Shoot-through protection	Configurable dead-time
Tied to VDDI or left open	Disabled	Disabled
Connected to GNDI via resistor $R_{DTC}$	Enabled	Enabled with $t_{dt} [ns] = 10 \times R_{DTC} [k\Omega]$ ; allowed $R_{DTC}$ range is 1k $\Omega$ to 100k $\Omega$
Connected to GNDI	Enabled	Disabled

The driver dead-time logic is triggered during the falling edge of an input and delays the rising transition of the other input. The delay is only assigned if the driver configured dead-time is longer than the inputs signals' own dead-time.

The dead-time can be configured by changing the current fed into the STP/DTC pin via an external resistance according to the formula:  $t_{dt} [ns] = 10 \times R_{DTC} [k\Omega]$ . It is recommended to use resistors with 1% accuracy in the 1 k $\Omega$  to 100 k $\Omega$  range. Connecting capacitors to the DTC pin must be avoided.



**Figure 4 Logic for STP/DTC pin connected to GNDI via resistance  $R_{DTC}$**

**Table 7 Logic for STP/DTC pin connected to GNDI via resistance  $R_{DTC}$**

Condition	STP/DTC logic
A, B	The driver logic assigns the configured dead-time since it is longer than the input signals' dead-time
C, D	The driver logic does not assign the configured dead-time since it is shorter than the input signals' dead-time
E, F	The shoot-through protection pulls down the outputs OUTA, OUTB until one of the outputs goes low. At this point, after the configured driver dead-time, the other output is allowed to go high



## 2 Functional description

### 2.5 Gate driver outputs

The rail-to-rail output stage realized with complementary MOS transistors is able to provide a typical 5 A sourcing and 9 A sinking peak current. The low on-resistance coming together with high driving current is particularly beneficial for fast switching of very large MOSFETs. With a  $R_{on}$  of  $\sim 1 \Omega$  for the sourcing pMOS and  $\sim 0.5 \Omega$  for the sinking nMOS transistor the driver can in most applications be considered as a nearly ideal switch. The p-channel sourcing transistor enables real rail-to-rail behavior without suffering from the voltage drop unavoidably associated with nMOS source follower stages.

In case of floating inputs or insufficient supply voltage not exceeding the UVLO thresholds, the driver outputs are actively clamped to the "low" level (GNDA, GNDB).

### 2.6 Fast active output clamping in UVLO conditions

The Undervoltage Lockout (UVLO) ensures that the gate driver output is not operated if the supplies are below the UVLO thresholds. However, this is not sufficient to guarantee that the output of the driver is kept low. Transients or noise in the power stage may pull-up the output node of the driver and the gate voltage causing an unwanted turn-on of the switch; this is particularly critical in system using bootstrapping since, during start-up, the supply of the high-side channel is delayed, while the low-side MOSFET is already switching. In resonant topologies (as LLC), the half-bridge switching node may be pulled up after the turn-off of the low-side switch. When the low-side MOSFET is turned on again, the high-side gate voltage increase induced by  $dV/dt$  event cannot be clamped by the driver  $R_{DS(on),sink}$  if the bootstrap supply is not yet available.

With a fast output clamping circuit in the output stage, the driver ensures safe operation against output induced overshoots in all UVLO situations. This structure allows fast reaction and effective clamping of the output pins (OUTA, OUTB). The exact reaction time depends on the output supply ( $V_{DDA}$ ,  $V_{DDB}$ ) and on the output voltage levels; however, already for very low supply levels ( $\sim 1$  V), the active output clamp is able to react in some tens of ns.

Undervoltage Lockout together with the output active clamping ensures that the outputs are actively held low in case of insufficient supply voltages.

**Table 8 Logic table in case of insufficient bias power - INA, INB, DISABLE**

Inputs		DIS	Supplies			Outputs	
INA	INB		$V_{DD}$	$V_{DDA}$	$V_{DDB}$	OUTA	OUTB
X	X	X	$< UVLO_{VDDI,on}$	X	X	L	L
X	X	X	$> UVLO_{VDDI,on}$	$< UVLO_{VDDI,on}$	$< UVLO_{VDDI,on}$	L	L
X	X	X	$> UVLO_{VDDI,on}$	$> UVLO_{VDDI,on}$	$< UVLO_{VDDI,on}$	Follows INA	L
X	X	X	$> UVLO_{VDDI,on}$	$< UVLO_{VDDI,on}$	$> UVLO_{VDDI,on}$	L	Follows INB

### 2.7 CT communication and input to output data transmission

A coreless transformer (CT) based communication module is used for PWM signal transfer between input and output. A proven high-resolution pulse repetition scheme in the transmitter combined with a watchdog timeout at the receiver side enables recovery from communication fails and ensures safe system shut-down in failure cases.

### 3 Electrical characteristics

## 3 Electrical characteristics

The absolute maximum ratings are listed in [Table 9](#). Stresses beyond these values may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### 3.1 Absolute maximum ratings

**Table 9 Absolute maximum ratings**

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
Input supply voltage	$V_{DDI}$	-0.3	–	18	V	–
Output supply voltage at pins VDDA, VDDDB	$V_{DDA}, V_{DDB}$	-0.3	–	22 <sup>1)</sup>	V	–
Voltage at pins INA, INB, DIS/EN (DC)	$V_{IN}$	-0.3	–	18	V	–
Voltage at pins INA, INB, DIS/EN (transient)	$V_{IN}$	-5	–	–	V	transient for 50 ns <sup>3)</sup>
Voltage at pin DTC	$V_{DTC}$	<sup>2)</sup>	–	$V_{DDI} + 0.3$	V	–
Voltage at pins OUTA, OUTB (DC)	$V_{OUT}$	-0.3	–	$V_{DDA/B} + 0.3$	V	–
Voltage at pins OUTA, OUTB (transient)	$V_{OUT}$	-2	–	$V_{DDA/B} + 1.5$	V	transient for 200 ns <sup>3)</sup>
Reverse current peak at pins OUTA, OUTB	$I_{SRC\_rev}$	-5	–	–	A <sub>pk</sub>	transient for 500 ns <sup>3)</sup>
Reverse current peak at pins OUTA, OUTB	$I_{SNK\_rev}$	–	–	5	A <sub>pk</sub>	transient for 500 ns <sup>3)</sup>
Junction temperature	$T_J$	-40	–	150	°C	–
Storage temperature	$T_{STG}$	-65	–	150	°C	–
Soldering temperature	$T_{SOL}$	–	–	260	°C	reflow <sup>4)</sup>
ESD capability	$V_{ESD\_CDM}$	–	–	0.5	kV	Charged Device Model (CDM) <sup>5)</sup>
ESD capability	$V_{ESD\_HBM}$	–	–	2	kV	Human Body Model (HBM) <sup>6)</sup>

- 1) Maximum positive supply voltage already complies with derating guidelines.
- 2) Minimum is given by internal regulation when DTC is operating (DTC pin connected to GND via resistance).
- 3) Not subject to production test - verified by design/characterization.
- 4) According to JEDEC-020E.
- 5) According to ANSI/ESDA/JEDEC JS-002.
- 6) According to ANSI/ESDA/JEDEC JS-001 (discharging 100 pF capacitor through 1.5 kΩ resistor).

### 3 Electrical characteristics

#### 3.2 Thermal characteristics

Thermal characteristics are obtained from simulation with 65 mW applied to the driver input-side and 200 mW applied to any output channel.

**Table 10 Thermal characteristics at  $T_A = 25^\circ\text{C}$**

Parameter	Symbol	Value		Unit	Note or condition
		1s0p <sup>1)</sup>	2s2p <sup>2)</sup>		
Thermal resistance junction-case (top) <sup>3)</sup>	$R_{thJC}$	46	46	K/W	–
Thermal resistance junction ambient <sup>4)</sup>	$R_{thJA25}$	107	69	K/W	–
	$R_{thJA85}$	95	65	K/W	–
Thermal resistance junction board <sup>5)</sup>	$R_{thJB}$	–	27	K/W	–
Characterization parameter junction-top <sup>6)</sup>	$\psi_{thJT}$	11	10	K/W	–
Characterization parameter junction-board <sup>6)</sup>	$\psi_{thJB25}$	21	23	K/W	–

1) Two-layer board as specified in JESD51-3 JEDEC-standard: no copper planes and no thermal vias for cooling, "package-alone" parameters

2) High-K board as specified in JESD51-7 JEDEC-standard: four-layers board with 2-oz inner layers copper planes and with no thermal vias for cooling

3) Obtained by simulating a cold plate test on the package top. No specific JEDEC standard exists, but a close description can be found in the ANSI SEMI standard G30-88

4) Obtained by simulating a JEDEC-standard, high-K board, as specified in JESD51-7, in an environment described in JESD51-2

5) Obtained by simulating a JEDEC-standard high-K board, as specified in JESD51-7, in an environment described in JESD51-8 with a ring cold plate fixture to control the PCB temperature

6) Estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining  $R_{th}$ , using a procedure described in JESD51-2a (sections 6 and 7)

### 3 Electrical characteristics

#### 3.3 Operating range

**Table 11** Operating range

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
Input supply voltage at pin VDDI	$V_{DDI}$	3	–	17	V	Min. defined by $UVLO_{VDDI}$
Output supply voltage at pin VDDA and VDDB	$V_{DDA}, V_{DDB}$	4.5	–	20 <sup>1)</sup>	V	4 V UVLO option
Output supply voltage at pin VDDA and VDDB	$V_{DDA}, V_{DDB}$	8.5	–	20 <sup>1)</sup>	V	8 V UVLO option
Output supply voltage at pin VDDA and VDDB	$V_{DDA}, V_{DDB}$	12.9	–	20 <sup>1)</sup>	V	12 V UVLO option
Output supply voltage at pin VDDA and VDDB	$V_{DDA}, V_{DDB}$	15.6	–	20 <sup>1)</sup>	V	15 V UVLO option
Input voltage at pins INA, INB, DIS/EN	$V_{IN}$	0	–	17	V	–
Input voltage at pin DTC	$V_{DTC}$	<sup>2)</sup>	–	$V_{DDI}$	V	–
Junction temperature	$T_J$	-40	–	150 <sup>3)</sup>	°C	
Ambient temperature	$T_A$	40	–	125	°C	–

1) Maximum positive supply voltage already complies with derating guidelines.

2) Minimum is given by internal regulation when DTC is operating (DTC pin connected to GND via resistance).

3) Continuous operation above 125°C may reduce lifetime.

#### 3.4 Electrical characteristics

Unless otherwise noted, the electrical characteristics are given for  $V_{DDI} = 3.3$  V,  $V_{DDA/B} = 12$  V and no load. Typical values are given at  $T_J = 25^\circ\text{C}$  whilst min. and max., instead, are the lower and upper limits, respectively, within the full operating range.

**Table 12** Power supply

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
IVDDI quiescent current	$I_{VDDIq}$	–	1.67	2.12	mA	no switching
IVDDA/B quiescent current	$I_{VDDA/Bq}$	–	0.62	0.86	mA	OUT = low, $V_{DDA/B} = 12$ V
IVDDA/B quiescent current	$I_{VDDA/Bq}$	–	0.66	0.89	mA	OUT = low, $V_{DDA/B} = 18$ V
IVDDA/B quiescent current	$I_{VDDA/Bq}$	–	0.76	1.0	mA	OUT = high, $V_{DDA/B} = 12$ V
IVDDA/B quiescent current	$I_{VDDA/Bq}$	–	0.9	1.14	mA	OUT = high, $V_{DDA/B} = 18$ V

### 3 Electrical characteristics

**Table 13 Undervoltage Lockout VDDI**

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
Undervoltage Lockout (UVLO) turn-on threshold VDDI	UVLO <sub>VDDI,on</sub>	–	2.85	2.95	V	–
Undervoltage Lockout (UVLO) turn-off threshold VDDI	UVLO <sub>VDDI,off</sub>	2.55	2.7	–	V	–
UVLO threshold hysteresis VDDI	UVLO <sub>VDDI,hys</sub>	0.10	0.15	0.20	V	–

**Table 14 Undervoltage Lockout VDDA, VDDB for 4 V UVLO option**

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
Undervoltage Lockout (UVLO) turn-on threshold VDDA, VDDB	UVLO <sub>VDDA,on</sub> UVLO <sub>VDDB,on</sub>	–	4.2	4.4	V	–
Undervoltage Lockout (UVLO) turn-off threshold VDDA, VDDB	UVLO <sub>VDDA,off</sub> UVLO <sub>VDDB,off</sub>	3.7	3.9	–	V	–
UVLO threshold hysteresis VDDA, VDDB	UVLO <sub>VDDA,hys</sub> UVLO <sub>VDDB,hys</sub>	0.2	0.3	0.4	V	–

**Table 15 Undervoltage Lockout VDDA, VDDB for 8 V UVLO option**

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
Undervoltage Lockout (UVLO) turn-on threshold VDDA, VDDB	UVLO <sub>VDDA,on</sub> UVLO <sub>VDDB,on</sub>	–	8.0	8.5	V	–
Undervoltage Lockout (UVLO) turn-off threshold VDDA, VDDB	UVLO <sub>VDDA,off</sub> UVLO <sub>VDDB,off</sub>	6.6	7.0	–	V	–
UVLO threshold hysteresis VDDA, VDDB	UVLO <sub>VDDA,hys</sub> UVLO <sub>VDDB,hys</sub>	0.7	1	1.3	V	–

**Table 16 Undervoltage Lockout VDDA, VDDB for 12 V UVLO option**

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
Undervoltage Lockout (UVLO) turn-on threshold VDDA, VDDB	UVLO <sub>VDDA,on</sub> UVLO <sub>VDDB,on</sub>	–	12.2	12.8	V	–

(table continues...)

### 3 Electrical characteristics

**Table 16** (continued) **Undervoltage Lockout VDDA, VDDB for 12 V UVLO option**

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
Undervoltage Lockout (UVLO) turn-off threshold VDDA, VDDB	UVLO <sub>VDDA,off</sub> UVLO <sub>VDDB,off</sub>	10.8	11.5	–	V	–
UVLO threshold hysteresis VDDA, VDDB	UVLO <sub>VDDA,hys</sub> UVLO <sub>VDDB,hys</sub>	0.5	0.7	0.9	V	–

**Table 17** **Undervoltage Lockout VDDA, VDDB for 15 V UVLO option**

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
Undervoltage Lockout (UVLO) turn-on threshold VDDA, VDDB	UVLO <sub>VDDA,on</sub> UVLO <sub>VDDB,on</sub>	–	14.9	15.5	V	–
Undervoltage Lockout (UVLO) turn-off threshold VDDA, VDDB	UVLO <sub>VDDA,off</sub> UVLO <sub>VDDB,off</sub>	13.7	14.4	–	V	–
Duplicate of UVLO threshold hysteresis VDDA, VDDB	UVLO <sub>VDDA,hys</sub> UVLO <sub>VDDB,hys</sub>	0.3	0.5	0.7	V	–

**Table 18** **Logic inputs INA, INB, DISABLE**

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
Input voltage threshold for transition LH	V <sub>INH</sub>	–	2.0	2.36	V	–
Input voltage threshold for transition HL	V <sub>INL</sub>	0.9	1.2	–	V	–
Input voltage threshold hysteresis	V <sub>IN_hys</sub>	0.38	0.8	1.2	V	–
High-level input leakage current	I <sub>IN</sub>	–	22	27	μA	INA/INB pin tied to VDDI
Input pull-down resistor	R <sub>IN,PD</sub>	–	150	–	kΩ	–

**Table 19** **Dead-time control (DTC) and shoot-through protection (STP)**

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
Dead-time	t <sub>dt</sub>	85	100	115	ns	R <sub>DTC</sub> = 10 kΩ
Dead-time	t <sub>dt</sub>	255	300	345	ns	R <sub>DTC</sub> = 30 kΩ
Dead-time	t <sub>dt</sub>	800	950	1100	ns	R <sub>DTC</sub> = 100 kΩ <sup>1)</sup>

(table continues...)

### 3 Electrical characteristics

**Table 19** (continued) **Dead-time control (DTC) and shoot-through protection (STP)**

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
Channel-to-channel dead-time mismatch	$\Delta t_{dt,Ch-Ch}$	0	–	10	ns	$R_{DTC} = 10\text{ k}\Omega$
Channel-to-channel dead-time mismatch	$\Delta t_{dt,Ch-Ch}$	0	–	14	ns	$R_{DTC} = 30\text{ k}\Omega$
Channel-to-channel dead-time mismatch	$\Delta t_{dt,Ch-Ch}$	0	–	40	ns	$R_{DTC} = 100\text{ k}\Omega$ <sup>1)</sup>
Part-to-part dead-time mismatch	$\Delta t_{dt,p-p}$	0	–	20	ns	$R_{DTC} = 10\text{ k}\Omega$ <sup>2)</sup>
Part-to-part dead-time mismatch	$\Delta t_{dt,p-p}$	0	–	55	ns	$R_{DTC} = 30\text{ k}\Omega$ <sup>2)</sup>
Part-to-part dead-time mismatch	$\Delta t_{dt,p-p}$	0	–	105	ns	$R_{DTC} = 100\text{ k}\Omega$ <sup>1) 2)</sup>

1) Not subject to production test - verified by design/characterization.

2) The parameter gives the difference in the dead-time inserted from different samples under the same conditions, including same ambient temperature.

**Table 20** **Static output characteristics**

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
High-level (sourcing) output resistance	$R_{on\_SRC}$	0.6	0.95	1.5	$\Omega$	$I_{SRC} = 50\text{ mA}$
Peak sourcing output current	$I_{SRC\_pk}$	–	5	–	A	$C_{LOAD} = 22\text{ nF}$ <sup>1)</sup>
Low-level (sinking) output resistance	$R_{on\_SNK}$	0.24	0.39	0.62	$\Omega$	$I_{SNK} = 50\text{ mA}$
Peak sinking output current	$I_{SNK\_pk}$		-9	–	A	$C_{LOAD} = 22\text{ nF}$ <sup>1)</sup>

1) Not subject to production test - verified by design/characterization.

**Table 21** **Dynamic characteristics**

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
INx to OUTx turn-on propagation delay	$t_{PDOn,INx}$	33	38	47	ns	See <a href="#">Figure 5</a> , <a href="#">Figure 6</a>
INx to OUTx turn-off propagation delay	$t_{PDOff,INx}$	30	36	46	ns	See <a href="#">Figure 5</a> , <a href="#">Figure 6</a>

**(table continues...)**

### 3 Electrical characteristics

**Table 21** (continued) **Dynamic characteristics**

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
Part-to-part turn-on propagation delay mismatch	$\Delta t_{PD_{on,p-p}}$	0	–	6	ns	<sup>1)</sup>
Part-to-part turn-off propagation delay mismatch	$\Delta t_{PD_{off,p-p}}$	0	–	8	ns	<sup>1)</sup>
Channel-to-channel turn-on propagation delay mismatch	$t_{PD_{on,ChA-ChB}}$	-4	–	4	ns	<sup>2)</sup> See Figure 7
Channel-to-channel turn-off propagation delay mismatch	$\Delta t_{PD_{off,ChA-ChB}}$	-5.5	–	3	ns	<sup>2)</sup> See Figure 7
Pulse width distortion	$t_{PWD}$	-5	2	5.5	ns	<sup>3)</sup> See Figure 8
Channel turn-off to channel turn-on propagation delay mismatch	$t_{DTD}$	-5	-2	1	ns	<sup>4)</sup> <sup>5)</sup> See Figure 9
Rise time	$t_{rise}$	–	7.5	14	ns	<sup>6)</sup> $C_{LOAD} = 1.8 \text{ nF}$ , see Figure 10
Fall time	$t_{fall}$	–	6	11	ns	<sup>6)</sup> $C_{LOAD} = 1.8 \text{ nF}$ , see Figure 10
Minimum input pulse width that changes output state	$t_{PW}$	10	17	25	ns	See Figure 11
Input-side start-up time	$t_{START,VDDI}$	–	3.5	5	μs	<sup>6)</sup> see Figure 12
Input-side deactivation time	$t_{STOP,VDDI}$	600	750	–	ns	<sup>6)</sup> see Figure 12
Output-side start-up time	$t_{START,VDDA/B}$	–	2.5	5	μs	<sup>6)</sup> see Figure 13
Output-side deactivation time	$t_{STOP,VDDA/B}$	500	800	–	ns	<sup>6)</sup> see Figure 13

- 1) The parameter gives the difference in the propagation delay between different samples switching in the same direction under same conditions, including same ambient temperature; therefore, is an indication of the production spread. The limits given are valid for all channels combination:  $t_{PD\_ChA} - t_{PD\_ChA}$ ,  $t_{PD\_ChB} - t_{PD\_ChB}$ ,  $t_{PD\_ChA} - t_{PD\_ChB}$ ,  $t_{PD\_ChB} - t_{PD\_ChA}$ .
- 2) The parameter gives the difference in the propagation delay of channel A and channel B switching in the same direction in the same sample.
- 3) The parameter gives the difference between ON and OFF propagation delay in the same channel (ChA or ChB), in the same sample at same ambient temperature.
- 4) The parameter gives the difference between the ON propagation delay of one channel and the OFF propagation delay of the other channel, in the same sample at same room temperature. This parameter represents the distortion of the inputs dead-time only when the driver DTC is not used or not enforced otherwise, please refer to Table 19.
- 5) Not subject to production test - verified by characterization.
- 6) Not subject to production test - verified by design/characterization.



### 3 Electrical characteristics

**Table 22 Common-Mode Transient Immunity (CMTI)**

Parameter	Symbol	Values			Unit	Note or condition
		Min.	Typ.	Max.		
Static Common-Mode Transient Immunity	$ CM_{Static,H} $	150	–	–	V/ns	$V_{CM} = 1500\text{ V}$ ; INA, INB tied to $V_{DDI}$ (logic high inputs) <sup>1) 2)</sup>
Static Common-Mode Transient Immunity	$ CM_{Static,L} $	150	–	–	V/ns	$V_{CM} = 1500\text{ V}$ ; INA, INB tied to GNDI (logic low inputs) <sup>1) 2)</sup>

1) Minimum slew rate of a common-mode voltage that is able to cause an incorrect output signal

2) Verified by characterization according to VDE0884-11 standard definitions and test-methods

### 3.5 Isolation specifications

**Table 23 Isolation specifications**

Parameter	Symbol	Value	Unit	Note or condition
External input-to-output creepage <sup>1)</sup>	CRP	8	mm	Shortest distance over package surface from any input pin to any output pin according to IEC 60664-1
External input-to-output clearance <sup>1)</sup>	CLR	8	mm	Shortest distance in air from any input pin to any output pin according to IEC 60664-1
Comparative tracking index	CTI	> 400	V	According to DIN EN 60112 (VDE 0303-11)
Material group	–	II	–	According to IEC 60112
Pollution degree	–	II	–	According to IEC 60664-1
Overvoltage category (for reinforced isolation)	–	I - IV	–	Rated mains voltage $\leq 150\text{ V}_{RMS}$
	–	I - IV	–	Rated mains voltage $\leq 300\text{ V}_{RMS}$
	–	I - III	–	Rated mains voltage $\leq 600\text{ V}_{RMS}$

#### Input-to-output isolation according to UL1577 Ed.5 <sup>2)</sup>

Input-to-output isolation voltage	$V_{ISO}$	5700	$V_{RMS}$	$V_{TEST} = V_{ISO}$ for $t = 60\text{ s}$ (qualification); $V_{TEST} = 1.2 \times V_{ISO}$ for $t = 1\text{ s}$ (100% productive tests)
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#### Input-to-output isolation according to DIN VDE V0884-11 <sup>3)</sup> and IEC 60747-17 <sup>4)</sup>

Maximum impulse voltage	$V_{IMP}$	8000	$V_{pk}$	According to IEC 60664-1
Maximum rated transient isolation voltage	$V_{IOTM}$	8000	$V_{pk}$	$V_{TEST} = V_{IOTM}$ for $t_{ini} = 60\text{ s}$ (type tests and quarterly monitoring) $V_{TEST} = 1.2 \times V_{IOTM}$ for $t_{ini} = 1\text{ s}$ (100% productive tests)
Maximum rated repetitive isolation voltage	$V_{IORM}$	1767	$V_{pk}$	According to Time Dependent Dielectric Breakdown (TDDDB) Test for reinforced isolation

(table continues...)

### 3 Electrical characteristics

**Table 23** (continued) Isolation specifications

Parameter	Symbol	Value	Unit	Note or condition
Apparent charge	$Q_{PD}$	< 5	pC	$V_{ini,b1} = 1.2 \times V_{IOTM}$ (100% productive tests) and $V_{ini,b1} = V_{IOTM}$ (type tests preconditioning) for $t_{ini} = 1s$ $V_{pd(m)} = 1.875 \times V_{IORM}$ for $t_m = 1 s$ <sup>5)</sup>
				After subgroup 1 life tests (type test) and in quarterly monitoring $V_{ini,a} = V_{IOTM}$ for $t_{ini} = 60 s$ $V_{pd(m)} = 1.6 \times V_{IORM}$ for $t_m = 10 s$
				After subgroup 2, 3 endurance tests (type test) $V_{ini,a} = V_{IOTM}$ for $t_{ini} = 60 s$ $V_{pd(m)} = 1.2 \times V_{IORM}$ for $t_m = 10 s$
Maximum surge isolation voltage <sup>6)</sup>	$V_{IOSM}$	6875	$V_{pk}$	$V_{IOSM\_TEST} = 1.6 \times V_{IOSM}$ for reinforced isolation according VDE 0884-11
		11000	$V_{pk}$	$V_{IOSM\_TEST} = 11 kV_{pk} \geq 1.3 \times V_{IOSM}$ for reinforced isolation according IEC 60747-17
Isolation resistance input-to-output <sup>7)</sup>	$R_{IO}$	$10^{12}$	$\Omega$	$V_{IO} = 500 V_{dc}$ for $t = 60 s$ , $T_A = 25^\circ C$ (type tests subgroup 1)
		$10^{11}$	$\Omega$	$V_{IO} = 500 V_{dc}$ for $t = 60 s$ , $T_A = 125^\circ C$ (type tests preconditioning, type test subgroup 4 and quarterly monitoring)
		$10^9$	$\Omega$	$V_{IO} = 500 V_{dc}$ for $t = 60 s$ , $T_A = 25^\circ C$ (type tests subgroup 1, 2, 3) or $T_A = T_S$ (type tests subgroup 4 and quarterly monitoring)
Capacitance input-to-output <sup>7)</sup>	$C_{IO}$	2	pF	$f = 1 MHz$

1) Creepage and clearance requirements depend on the application and related end-equipment isolation standard. Care should be taken to keep the required creepage and clearance value on printed-circuit-board level.

2) See UL 1577 certificate n. E311313.

3) See VDE 0884-11 certificate n. 40052310.

4) See IEC 60747-17 certificate n. 40055138.

5) The partial discharge voltage  $VPD(m)$  applied during production tests is greater ( $4411 V_{pk} > 1.875 \times V_{IORM}$ ) to include the F4 factor required by end equipment standards IEC 60664-1, IEC 62368-1 ( $VPD(m) = F1 \times F2 \times F3 \times F4 \times V_{IORM} = 1.875 \times F4 \times V_{IORM}$ ).

6) The surge test is performed in insulation oil to determine the intrinsic surge immunity of the insulation barrier.

7) The parameters apply to the product converted in a two terminals device with all terminals on side 1 connected together and all terminals on side 2 connected together.

**Table 24** Output channel-to-channel isolation specifications

Parameter	Symbol	Value	Unit	Note or condition
External channel-to-channel creepage <sup>1)</sup>	$CRP_{Ch-Ch, 14pin}$	3.3	mm	Shortest distance over package surface between any output

(table continues...)

### 3 Electrical characteristics

**Table 24** (continued) **Output channel-to-channel isolation specifications**

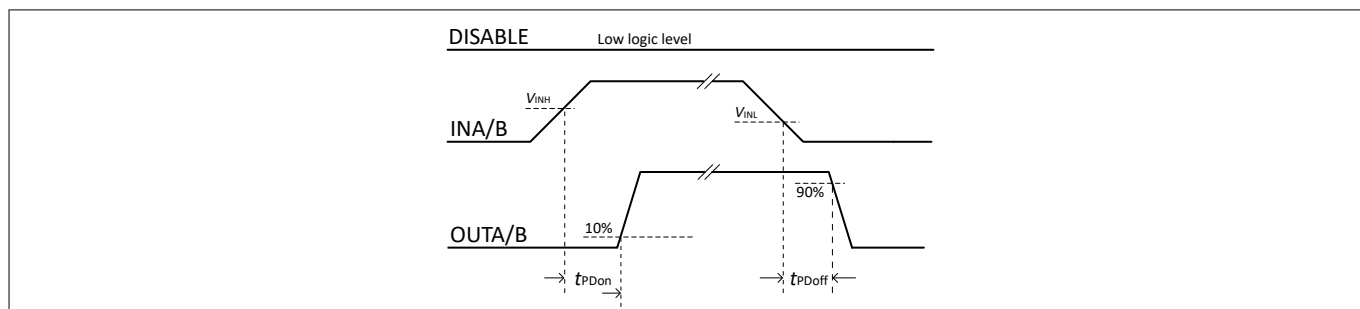
Parameter	Symbol	Value	Unit	Note or condition
	CRP <sub>Ch-Ch, 16pin</sub>	2.5	mm	channel A pin and any output channel B pin

1) Creepage and clearance requirements depend on the application and related end-equipment isolation standard. Care should be taken to keep the required creepage and clearance value on printed-circuit-board level

## 4 Timing diagrams

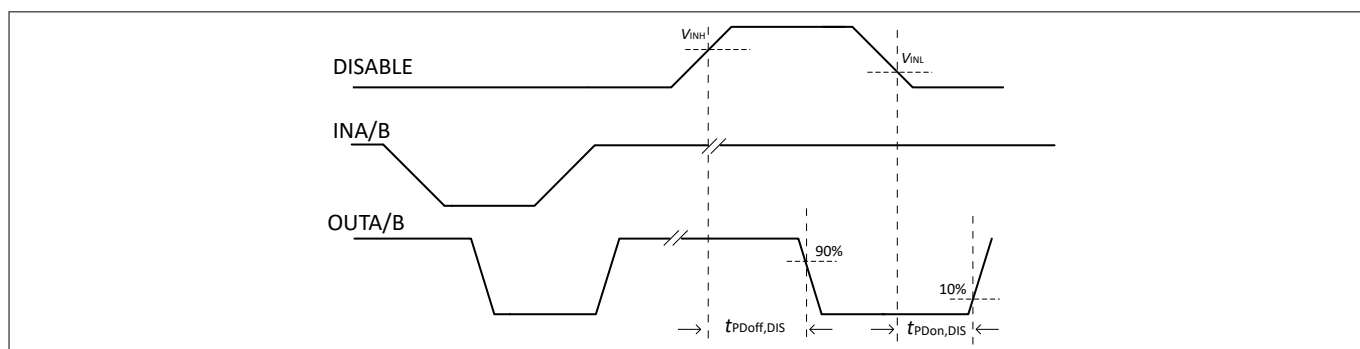
### 4 Timing diagrams

Figure 5 illustrates the input-to-output propagation delays as observed at the capacitively loaded output.



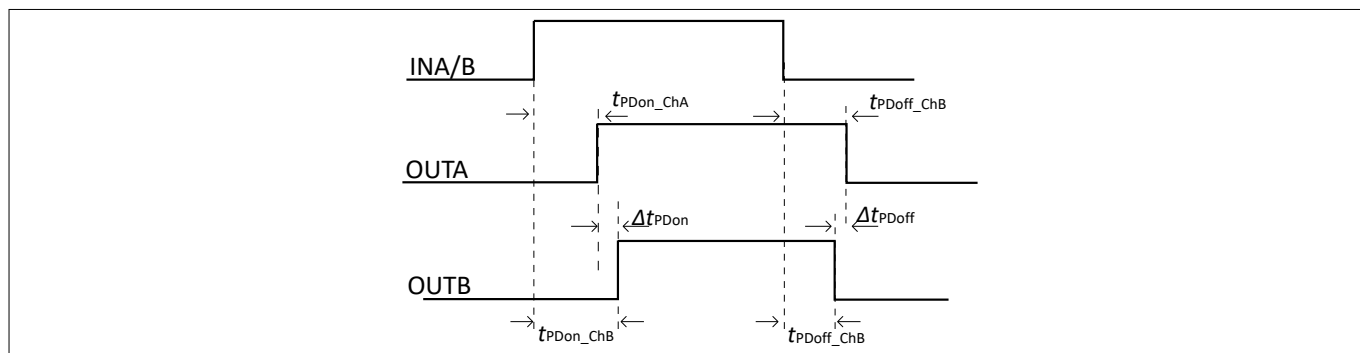
**Figure 5** INx to OUTx propagation delays

Figure 6 illustrates the disable-to-output propagation delays as observed at the capacitively loaded output.



**Figure 6** DISABLE to OUTx propagation delays

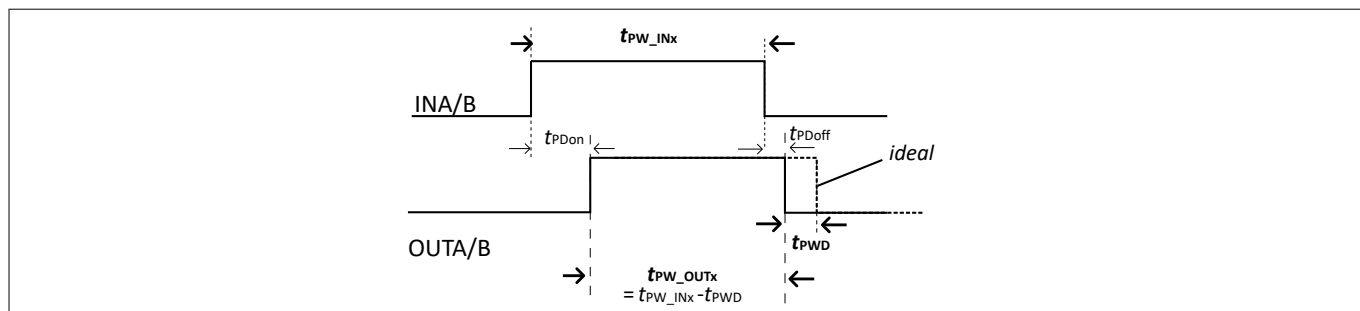
Figure 7 illustrates the channel-to-channel propagation delay mismatch at the unloaded outputs. This parameter is relevant when the channels drive parallel switches as it represents the delay in the two driving signals.



**Figure 7** Channel-to-channel propagation delay mismatch

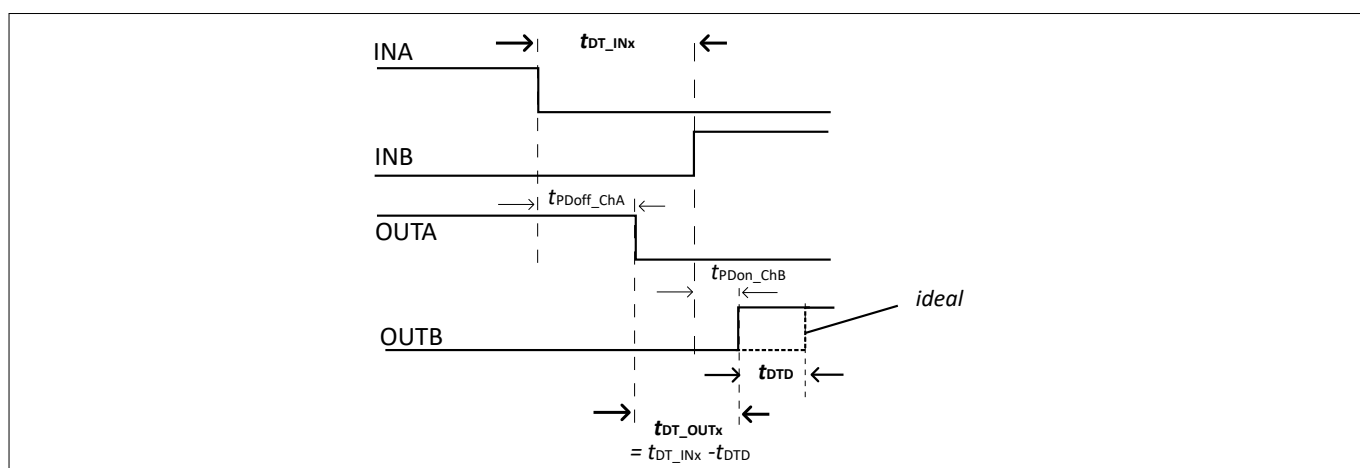
Figure 8 illustrates the pulse width distortion at the unloaded output. Ideally the width of the input pulse ( $t_{PW\_INx}$ ) equals the width of the output pulse ( $t_{PW\_OUTx}$ ); however, the driver introduces an output pulse distortion  $t_{PW}$  given by the difference between ON and OFF propagation delay.

## 4 Timing diagrams



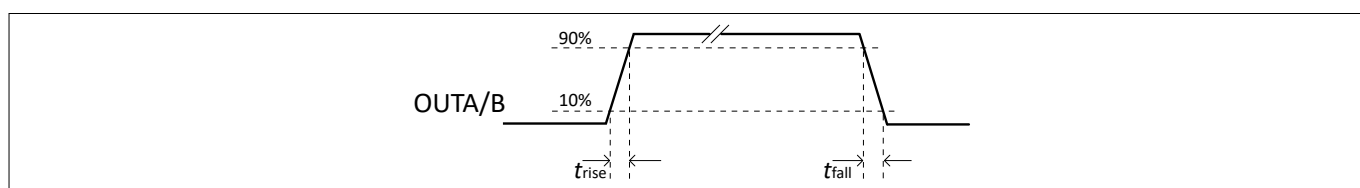
**Figure 8 Pulse width distortion**

Figure 9 illustrates the dead-time distortion at the unloaded outputs. This parameter is relevant in operation with complementary signals, as for the half-bridge driving when a certain dead-time  $t_{DT\_INx}$  is set on the inputs INA, INB. Ideally the dead-time on the driver output ( $t_{DT\_OUTx}$ ) equals the input dead-time; however, the driver introduces a distortion  $t_{DTc}$  given by the difference between the OFF propagation delay of one channel and the ON propagation delay of the other channel.



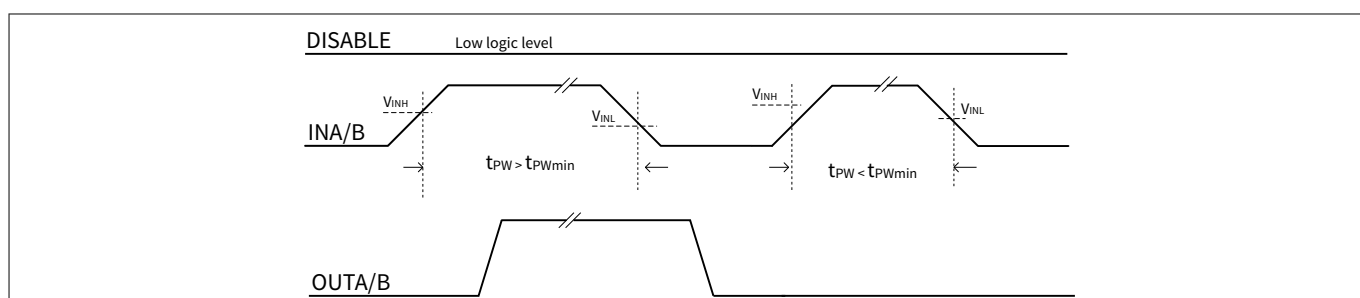
**Figure 9 Channel turn-off to channel turn-on propagation delay mismatch**

Figure 10 illustrates the rise and fall time as observed at the capacitively loaded output.



**Figure 10 Rise and fall time**

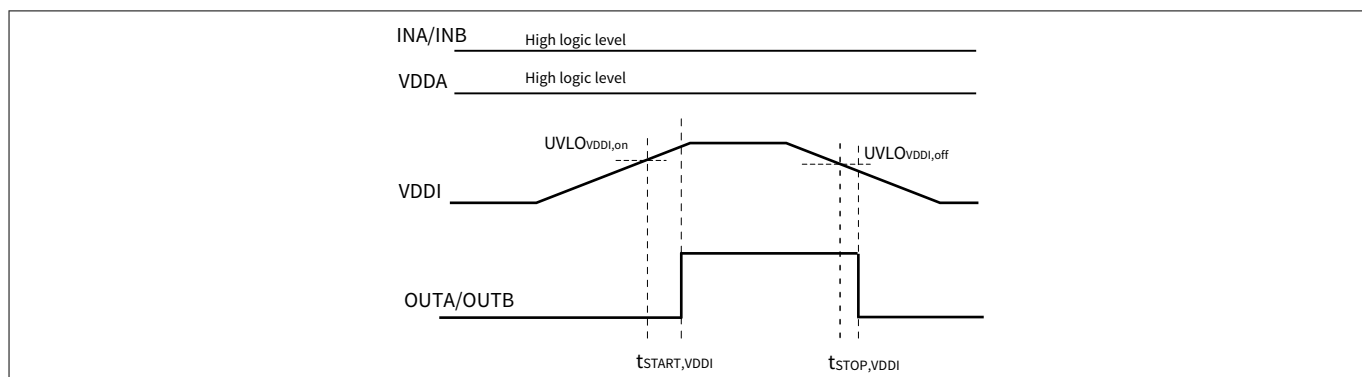
Figure 8 illustrates the behavior of the deglitch filter that filters spurious pulses on INA, INB with duration shorter than  $t_{PWmin}$ .



**Figure 11 Minimum pulse that changes the output state**

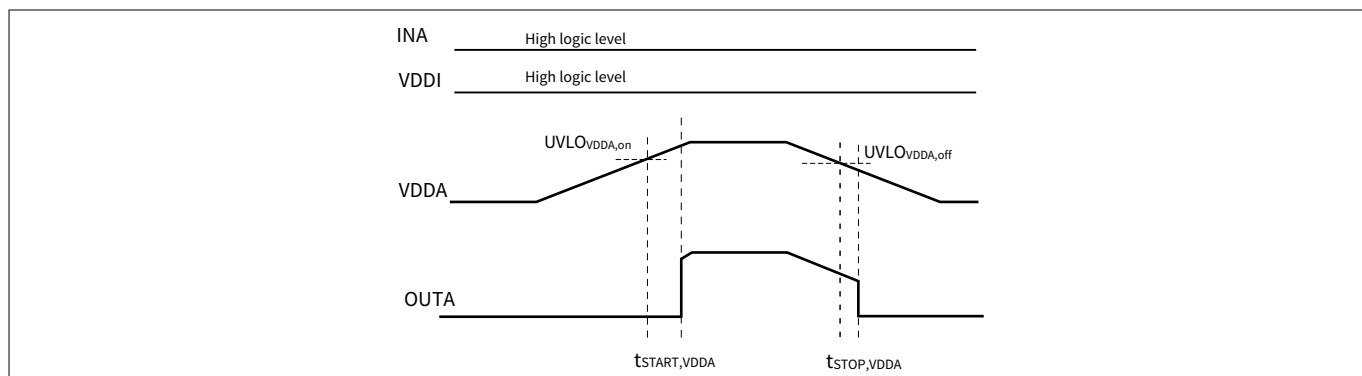
## 4 Timing diagrams

Figure 12 illustrates the input-side supply UVLO behavior. It depicts the reaction time to UVLO events when  $V_{DDI}$  crosses the UVLO thresholds during rising or falling transitions (power-up, power-down, supply noise).



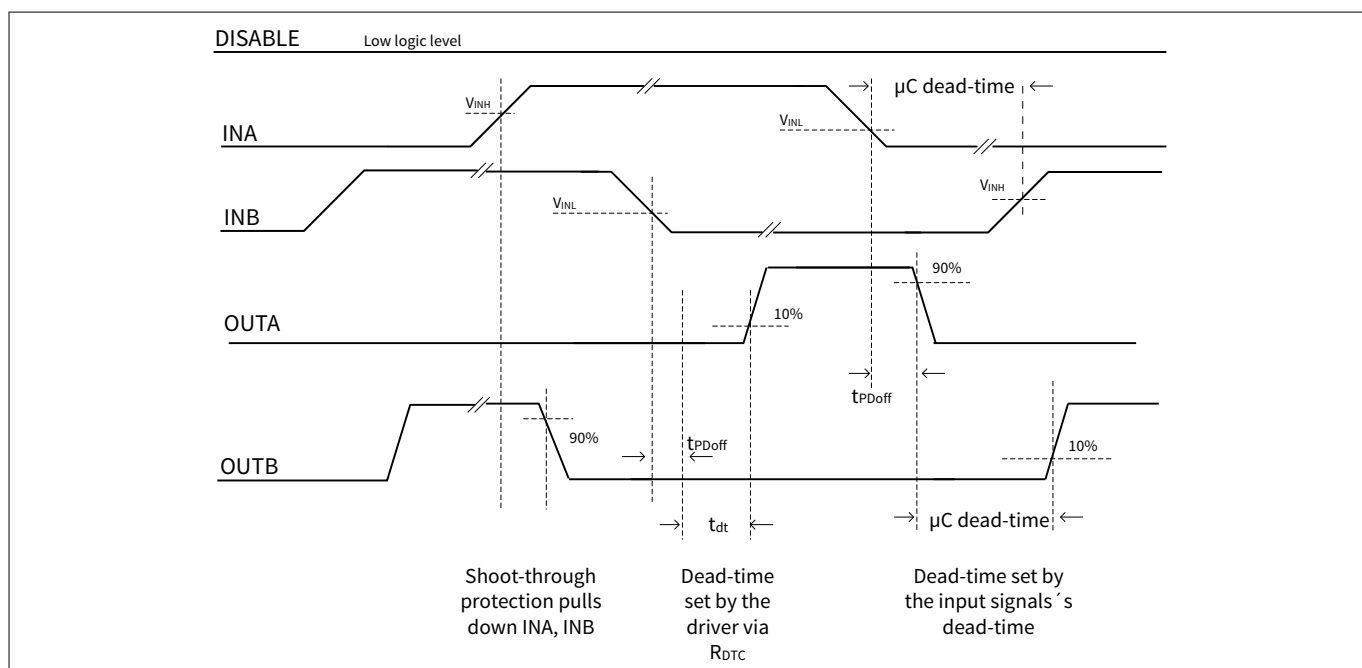
**Figure 12**  $V_{DDI}$  UVLO behavior, start-up and deactivation time

Figure 13 illustrates the output-side supply UVLO behavior. It depicts the reaction time to UVLO events when  $V_{DDA/B}$  crosses the UVLO thresholds during rising or falling transitions (power-up, power-down, supply noise).



**Figure 13**  $V_{DDA}, V_{DDB}$  UVLO behavior, start-up and deactivation time

Figure 14 illustrates the shoot-through protection and dead-time logic. When enabled, the dead-time is added on top of the turn-off propagation delay if the driver dead-time is longer than the signals' own dead-time.

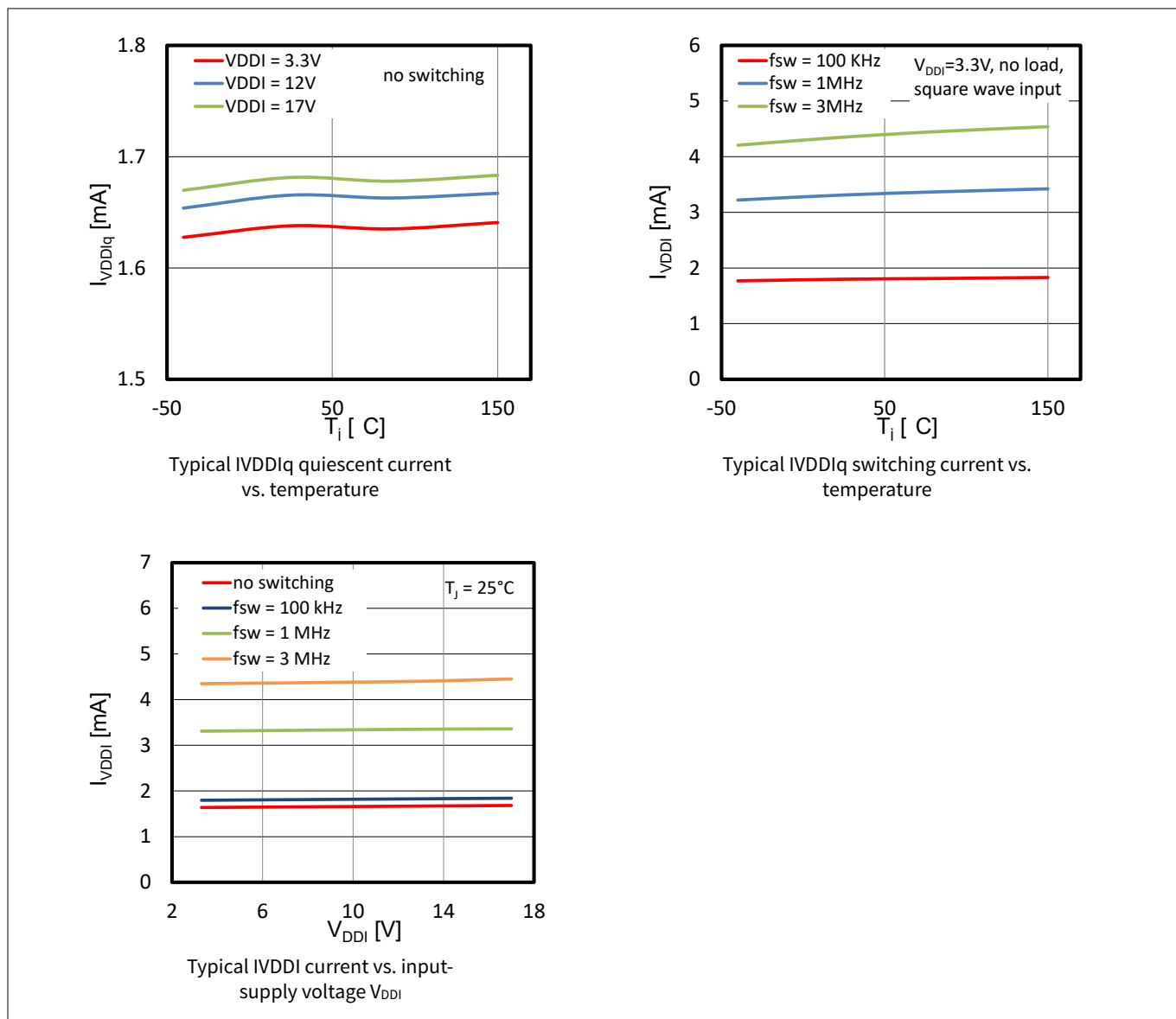


**Figure 14** Shoot-through and configurable dead-time

## 5 Typical characteristics

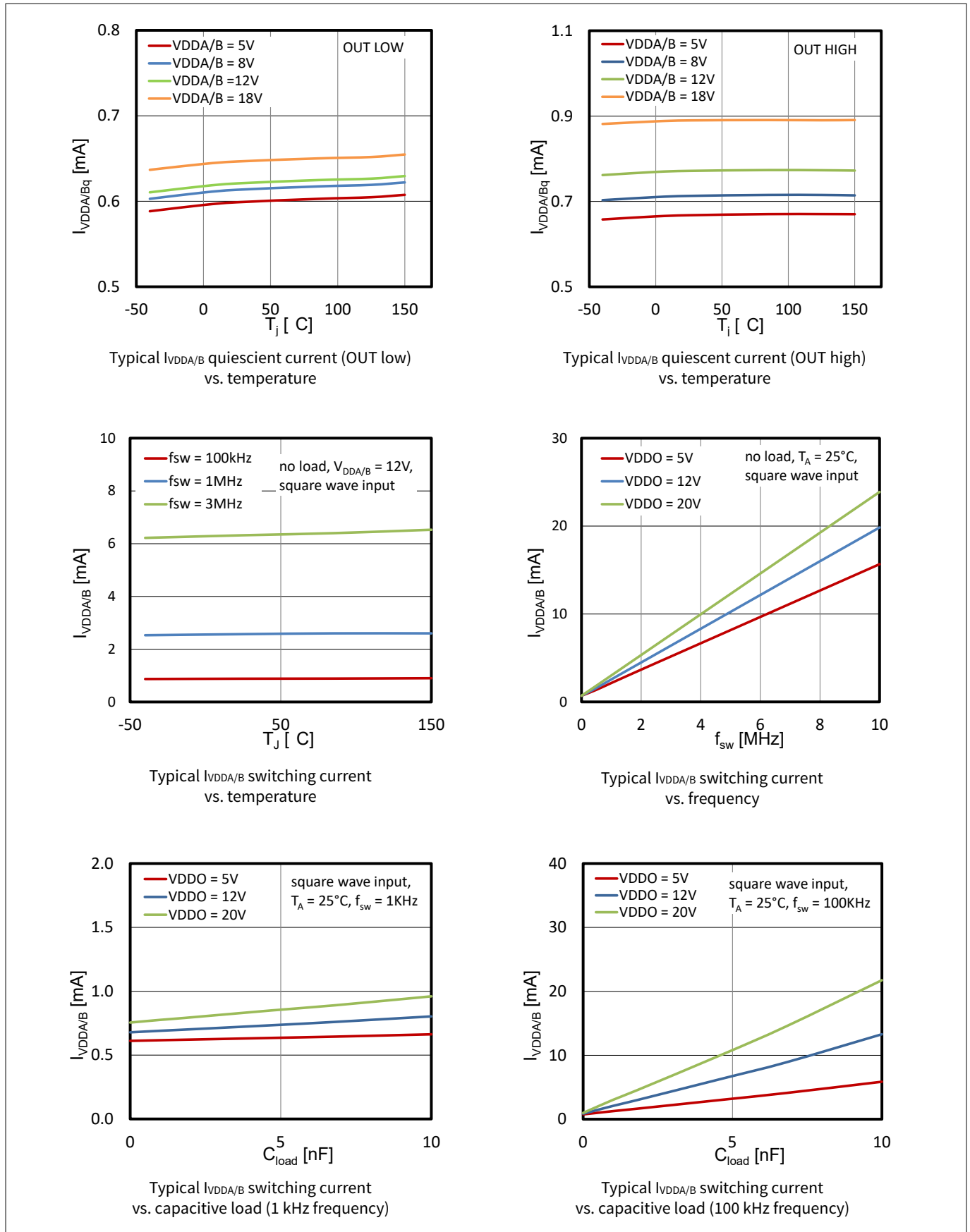
### 5 Typical characteristics

$V_{DDI} = 3.3\text{ V}$ ,  $V_{DDA/B} = 12\text{ V}$ ,  $T_A = 25^\circ\text{C}$ ,  $f_{sw} = 1\text{ MHz}$ , no load unless otherwise noted



**Figure 15** Input-side supply current

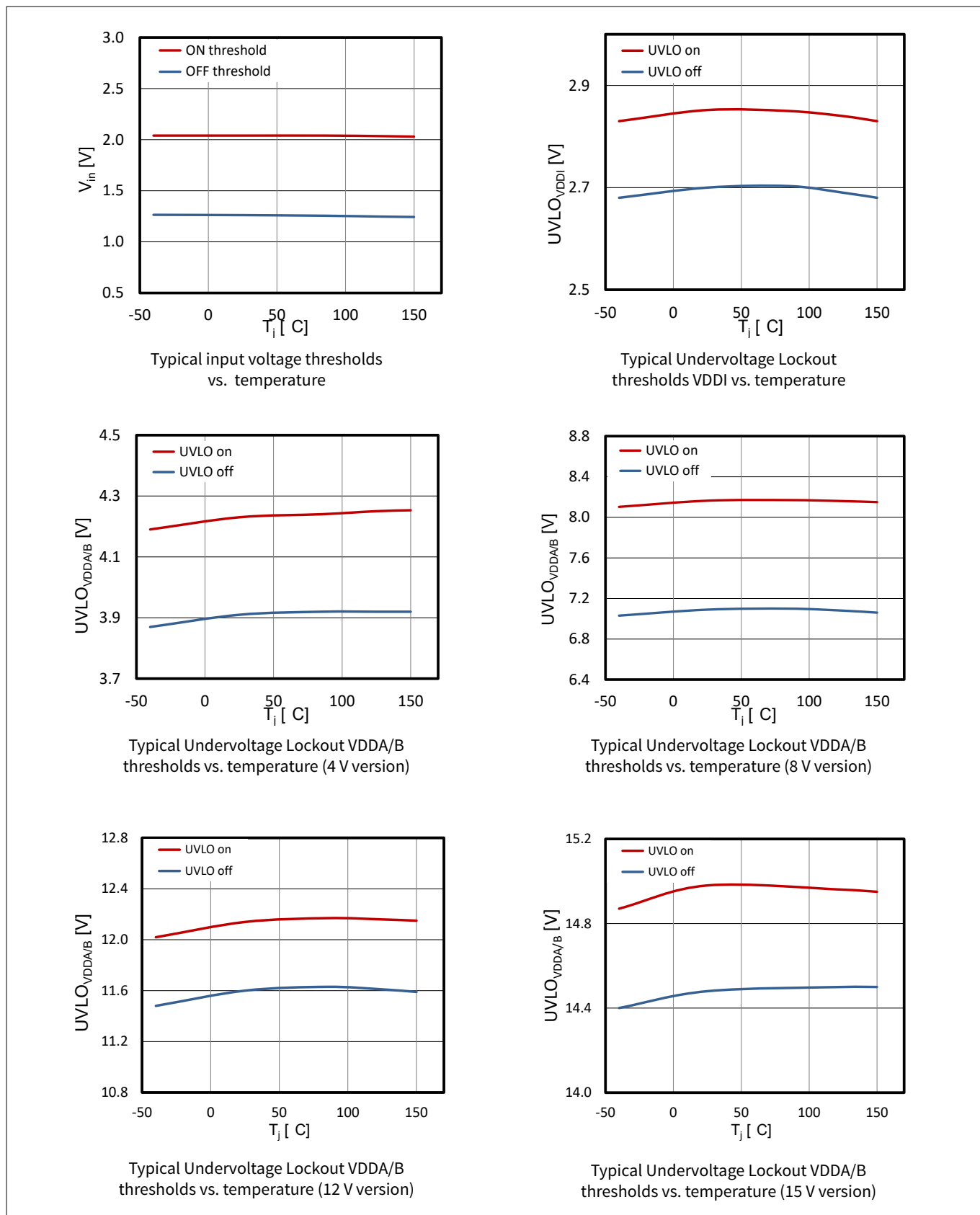
## 5 Typical characteristics



**Figure 16** Output-side supply current

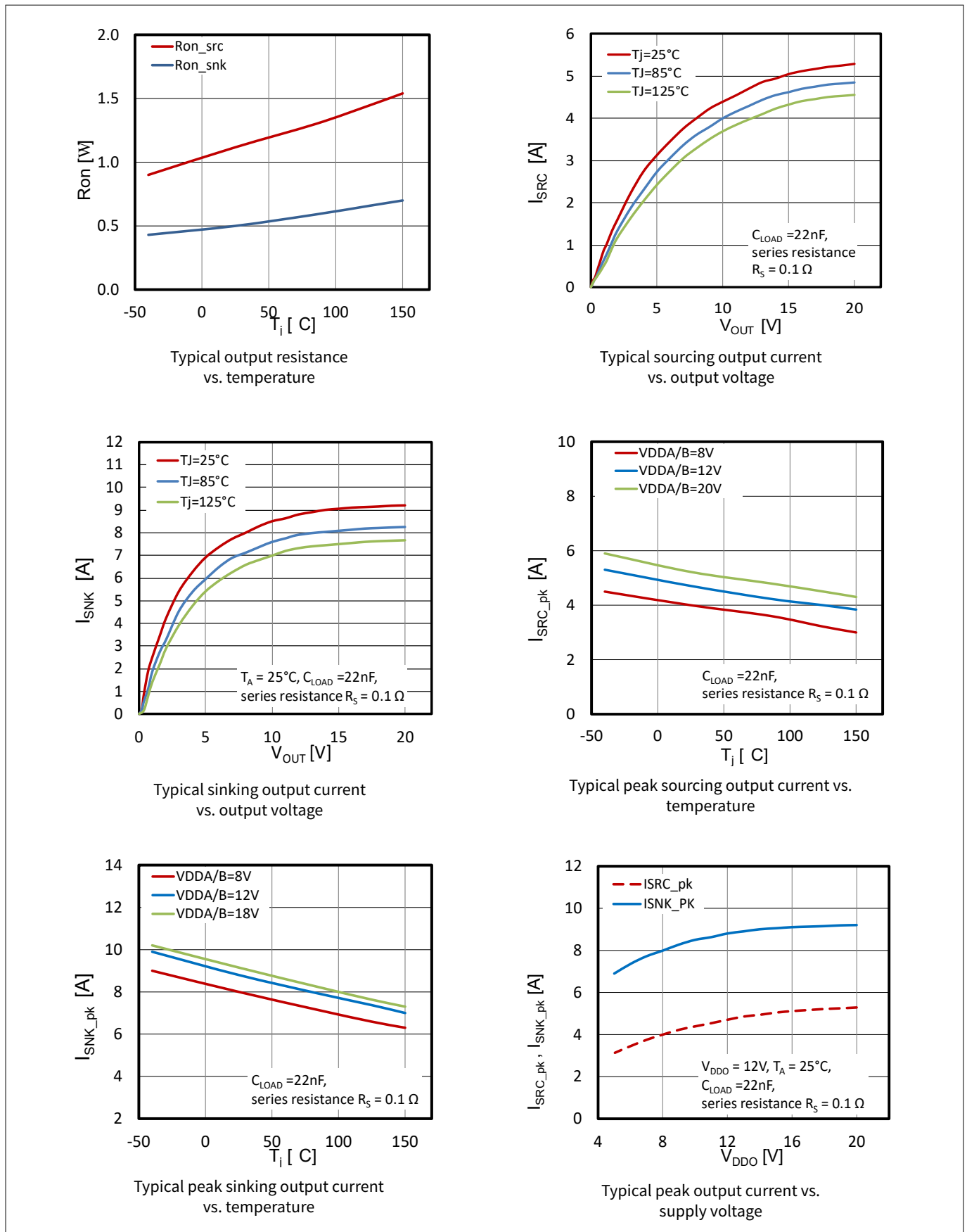


## 5 Typical characteristics



**Figure 17** Input voltage thresholds and Undervoltage Lockout

## 5 Typical characteristics



**Figure 18** Typical output static characteristics

5 Typical characteristics

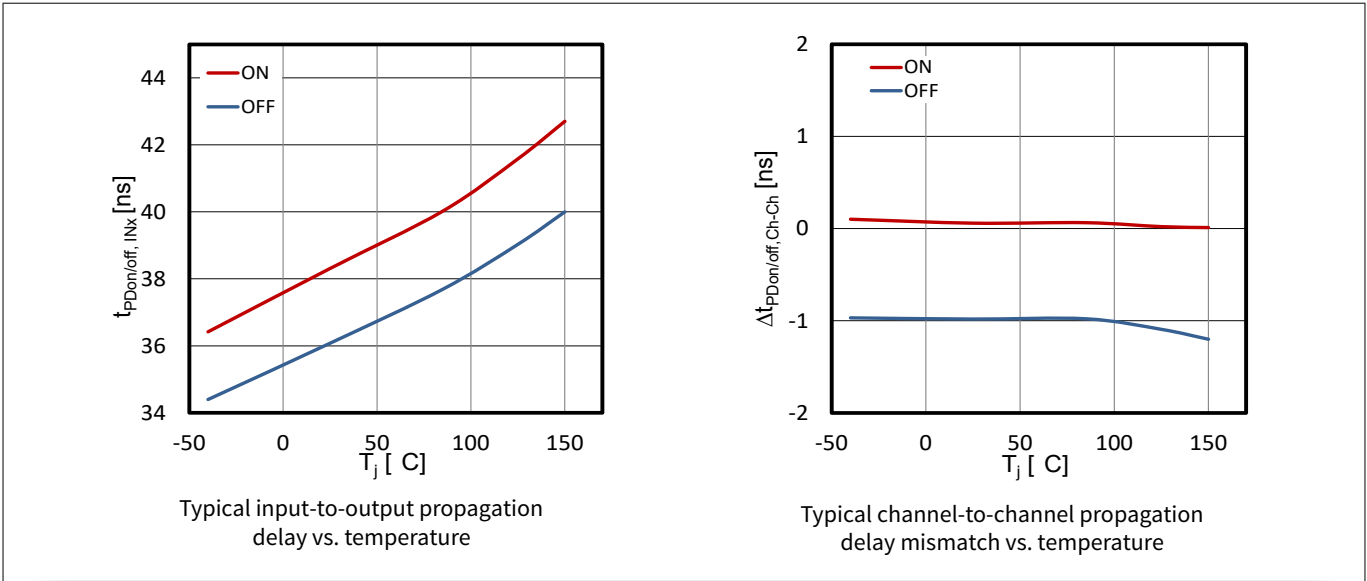
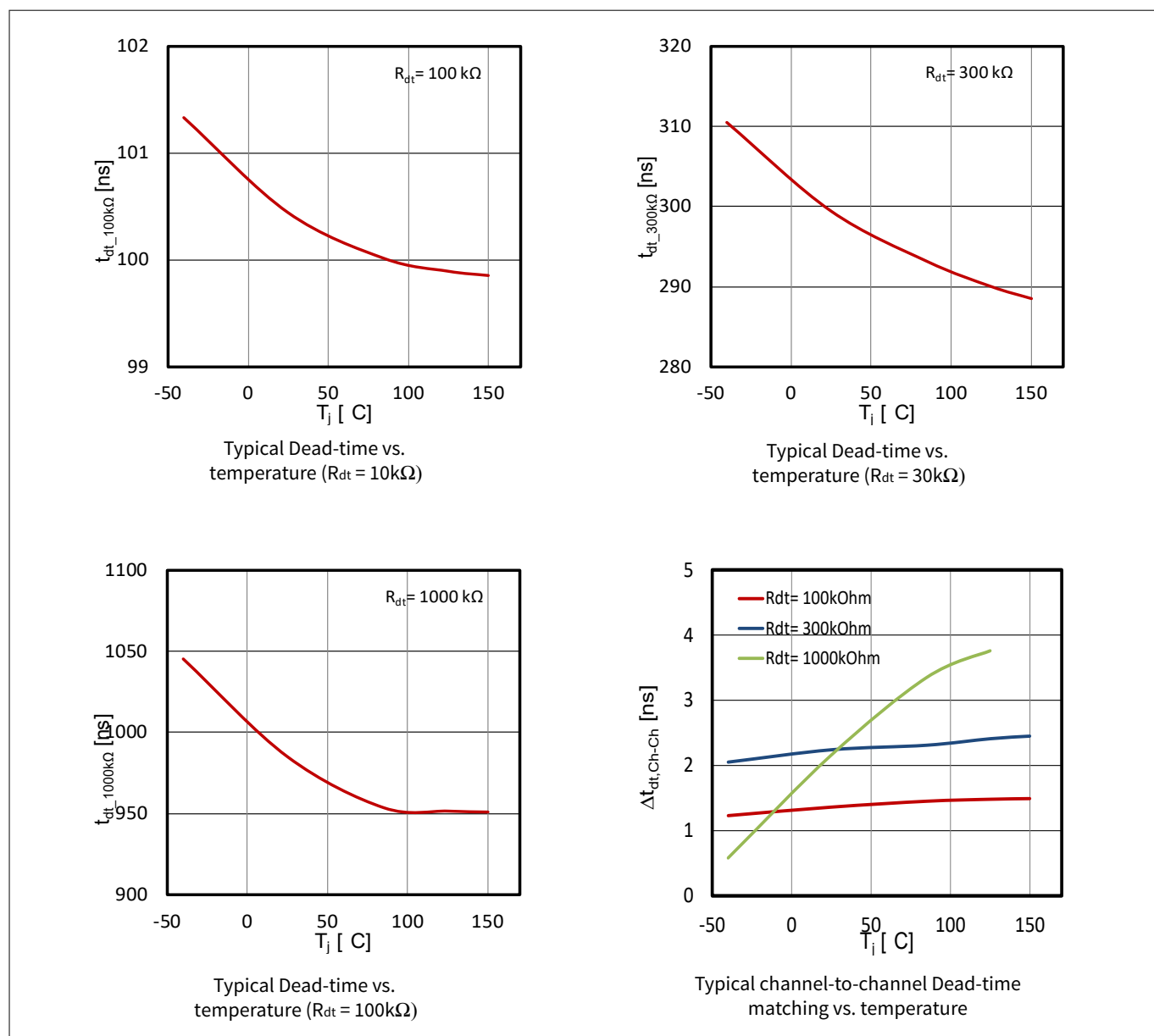


Figure 19 Typical propagation delays

## 5 Typical characteristics



**Figure 20** Typical dead-time

## 6 Package outline dimensions

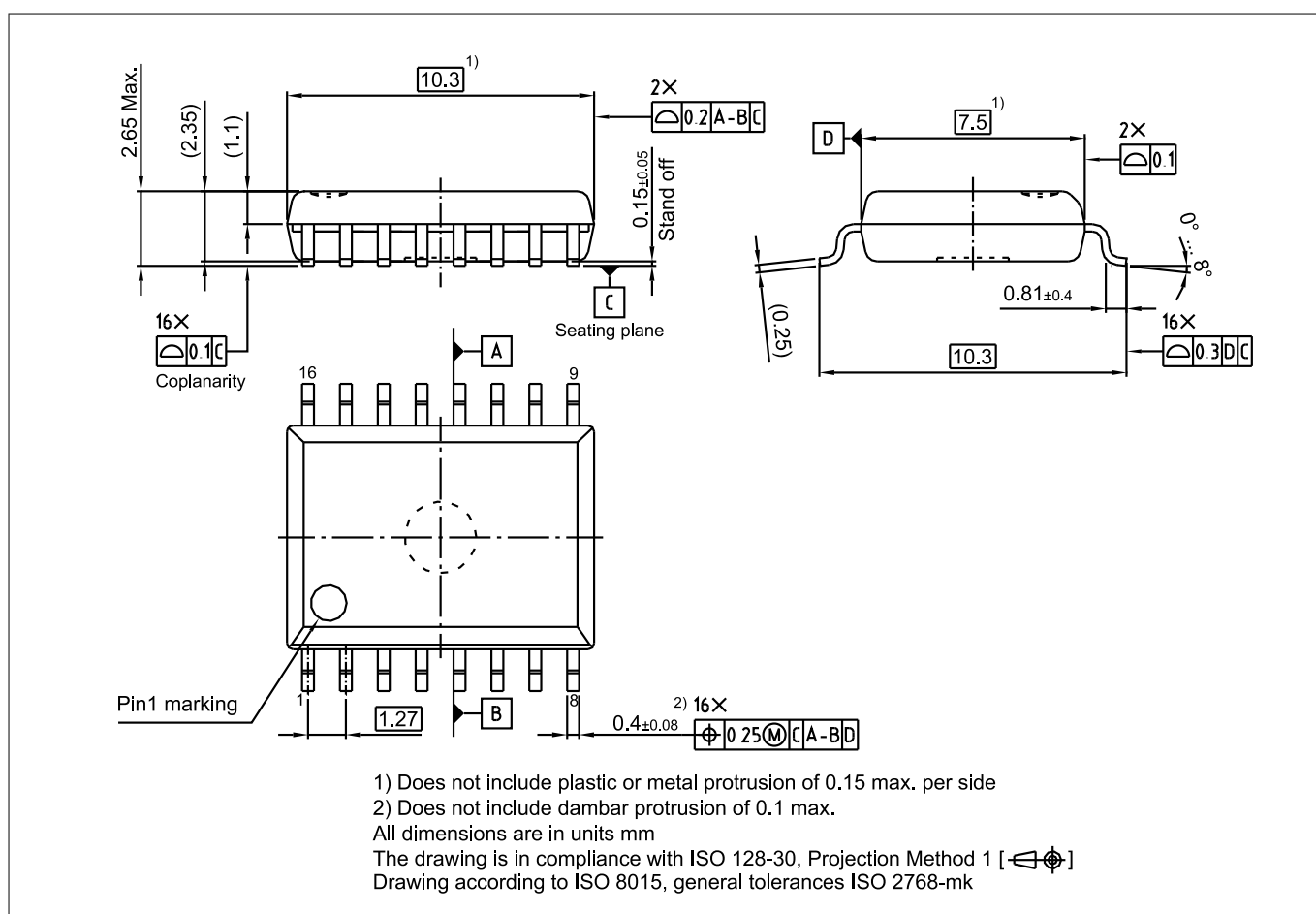
### 6 Package outline dimensions

#### 6.1 Device numbers and markings

**Table 25** Device numbers and markings

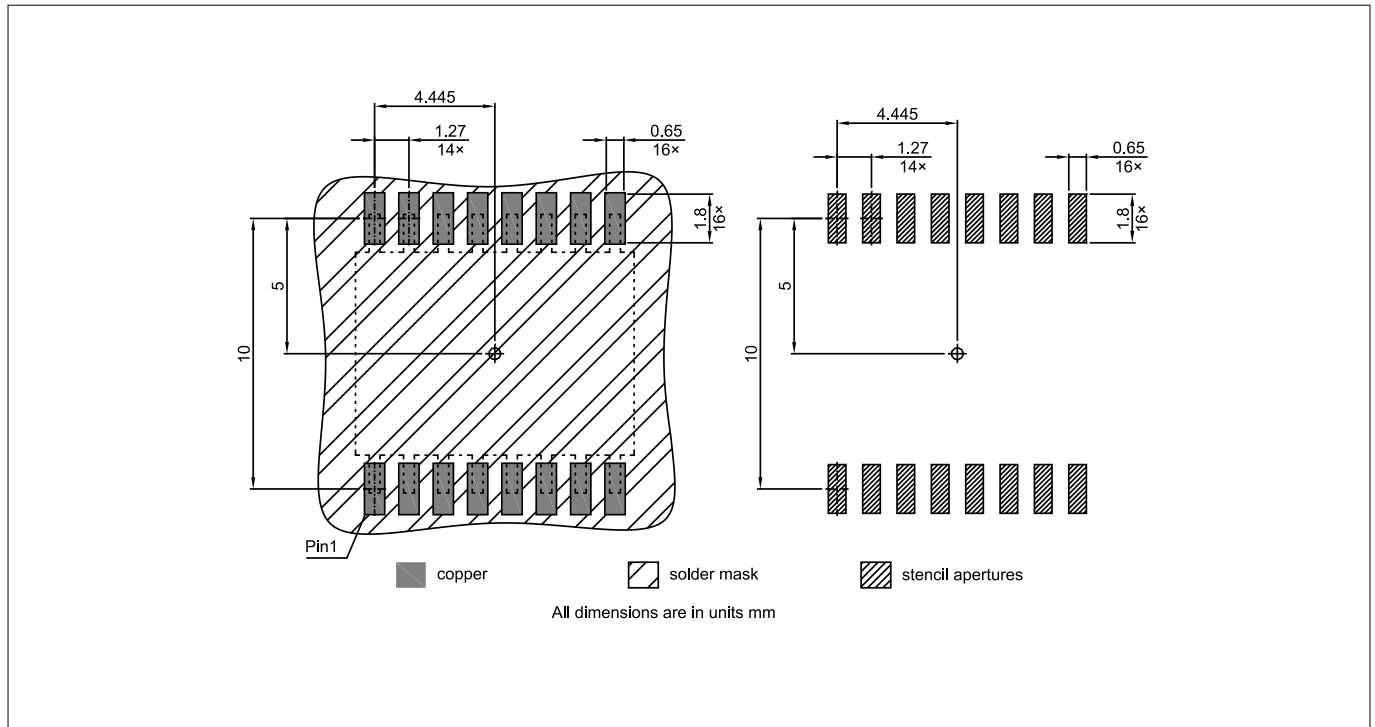
Part number	Orderable part number (OPN)	Device marking
2EDR8259H	2EDR8259HXUMA1	2R8259A
2EDR7259X	2EDR7259XXUMA1	2R7259A
2EDR8259X	2EDR8259XXUMA1	2R8259A
2EDR9259X	2EDR9259XXUMA1	2R9259A
2EDR6258X	2EDR6258XXUMA1	2R6258A
2EDR8258X	2EDR8258XXUMA1	2R8258A
2EDR9258X	2EDR9258XXUMA1	2R9258A

#### 6.2 Package DSO16-300mil

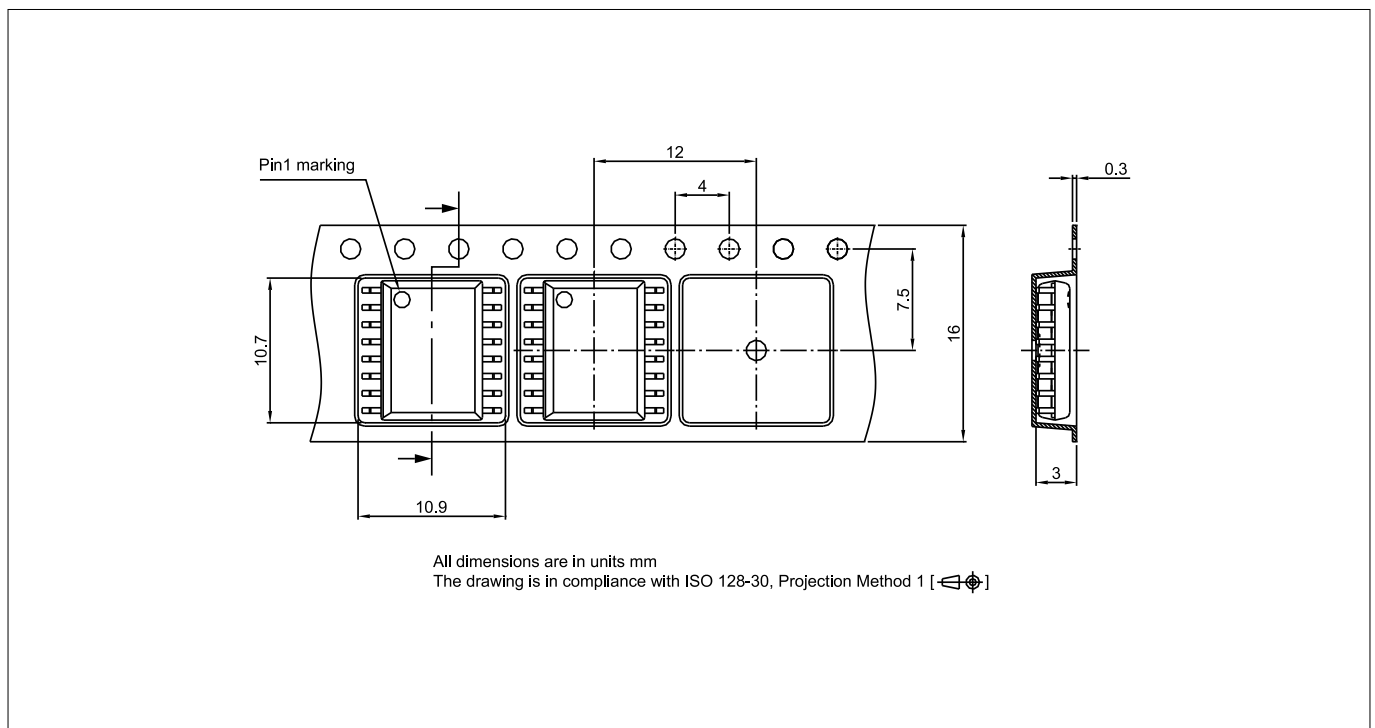


**Figure 21** DSO16-300mil outline

## 6 Package outline dimensions



**Figure 22** **DSO16-300mil footprint**



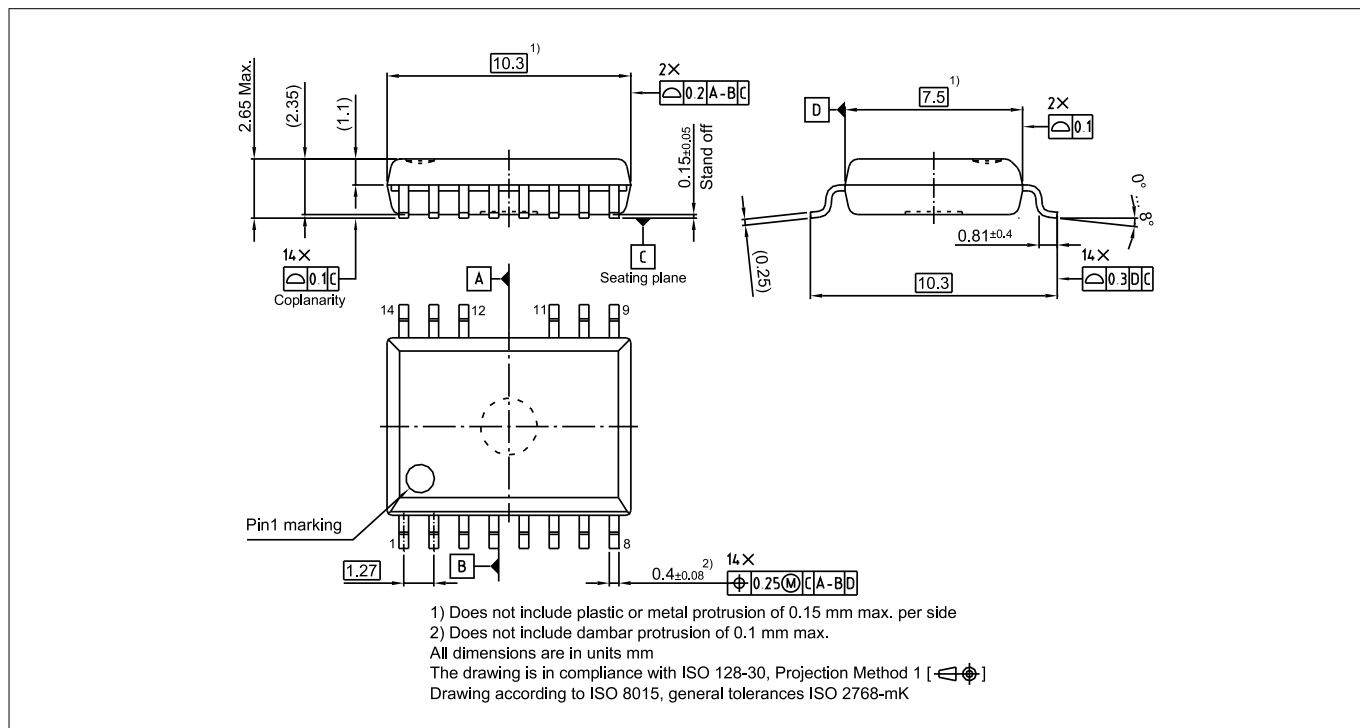
**Figure 23** **DSO16-300mil packing**

### Green Product (RoHS compliant)

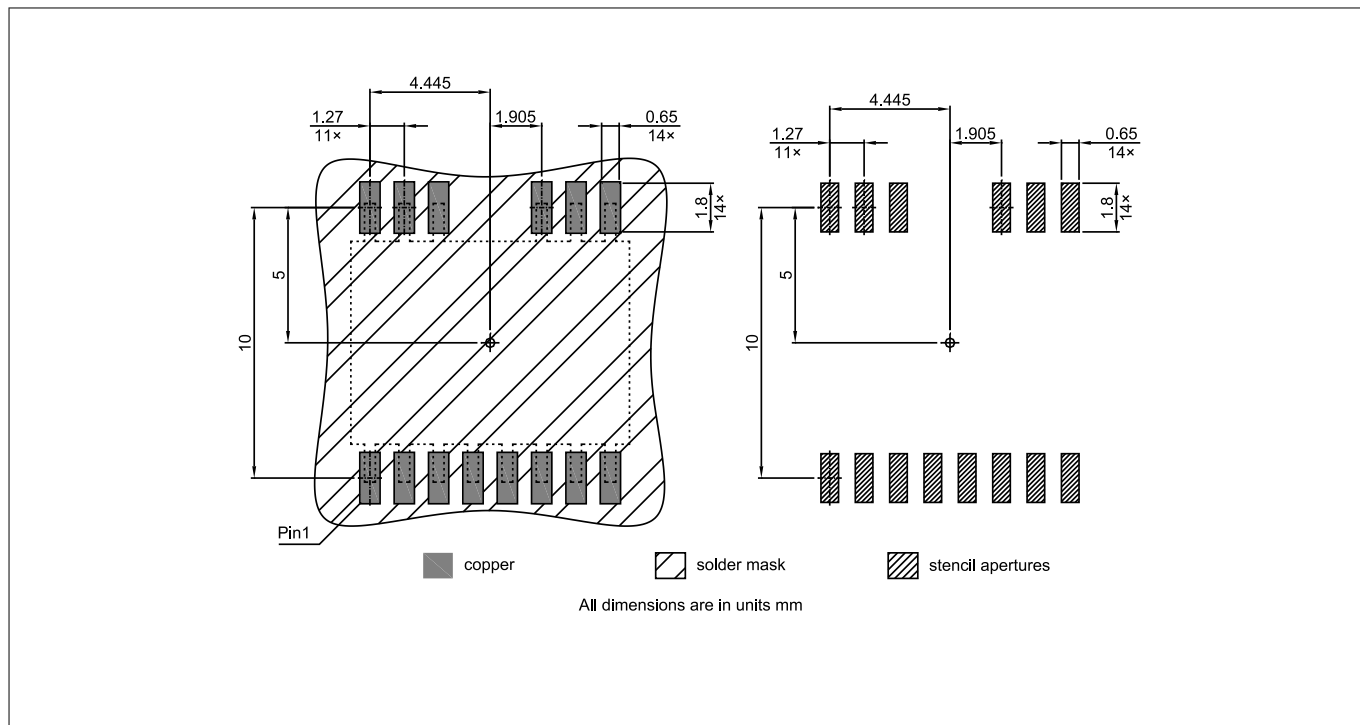
To meet the worldwide customer requirements for environmentally friendly products and to be compliant with government regulations the device is available as a green product. Green products are RoHS-Compliant (i.e. Pb-free finish on leads and suitable for Pb-free soldering according to IPC/JEDEC J-STD-020). Further information on packages: <https://www.infineon.com/packages>

## 6 Package outline dimensions

### 6.3 Package DSO14-300mil

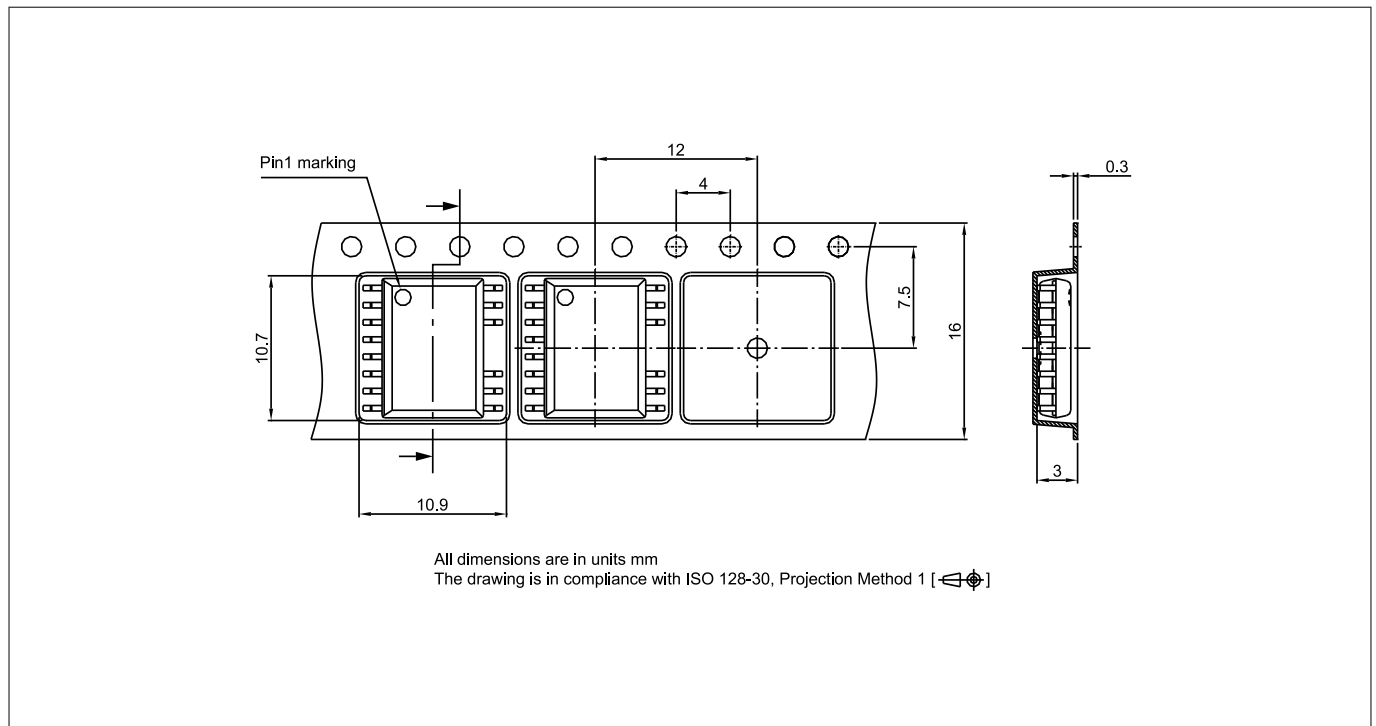


**Figure 24** DSO14-300mil outline



**Figure 25** DSO14-300mil footprint

## 6 Package outline dimensions



**Figure 26**      **DSO14-300mil packing**

### Green Product (RoHS compliant)

To meet the worldwide customer requirements for environmentally friendly products and to be compliant with government regulations the device is available as a green product. Green products are RoHS-Compliant (i.e. Pb-free finish on leads and suitable for Pb-free soldering according to IPC/JEDEC J-STD-020). Further information on packages: <https://www.infineon.com/packages>



## 7 Revision history

### 7 Revision history

Revision	Date	Description of changes
Rev 1.3	2023-02-27	Added condition "DTC pin connected to ground" Fixed typo in the OPN of <a href="#">Table 25</a>
Rev 1.2	2023-01-19	Fixed typo in channel-to-channel propagation delay mismatch
Rev 1.1	2022-12-12	Removed watermark "restricted" "Dead-time distortion" renamed as "Channel turn-off to channel turn-on propagation delay mismatch" in <a href="#">Table 21</a>
Rev 1.0	2022-12-09	Initial release

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